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MEMORY FOR PROGRAMMING DATA STATES OF MEMORY CELLS

Abstract

Memories might include a controller configured to cause the memory to precharge a data line and a node to a first voltage level, isolate the node from the data line then capacitively couple a boost voltage level to the node, selectively discharge the data line through a memory cell while applying a second voltage level to the memory cell, connect and then isolate the node and the data line, capacitively couple a deboost voltage level to the node, electrically float a control gate of a transistor that is connected to the node, connect a first source/drain of the transistor to the data line while applying a third voltage level to a second source/drain of the transistor and while electrically floating the control gate of the transistor, and apply a fourth voltage level to the memory cell while the data line is connected to the first source/drain of the transistor.

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Background/Summary

[0001] This application is a Divisional of U.S. application Ser. No. 17/894,248, titled “MEMORY FOR PROGRAMMING DATA STATES OF MEMORY CELLS,” filed Aug. 24, 2022, (Allowed) which is commonly assigned and incorporated herein by reference.

TECHNICAL FIELD

[0002] The present disclosure relates generally to memory and, in particular, in one or more embodiments, the present disclosure relates to apparatus and methods for programming data states of memory cells.

BACKGROUND

[0003] Memories (e.g., memory devices) are typically provided as internal, semiconductor, integrated circuit devices in computers or other electronic devices. There are many different types of memory including random-access memory (RAM), read only memory (ROM), dynamic random access memory (DRAM), synchronous dynamic random access memory (SDRAM), and flash memory.

[0004] Flash memory has developed into a popular source of non-volatile memory for a wide range of electronic applications. Flash memory typically use a one-transistor memory cell that allows for high memory densities, high reliability, and low power consumption. Changes in threshold voltage (Vt) of the memory cells, through programming (which is often referred to as writing) of charge storage structures (e.g., floating gates or charge traps) or other physical phenomena (e.g., phase change or polarization), determine the data state (e.g., data value) of each memory cell. Common uses for flash memory and other non-volatile memory include personal computers, personal digital assistants (PDAs), digital cameras, digital media players, digital recorders, games, appliances, vehicles, wireless devices, mobile telephones, and removable memory modules, and the uses for non-volatile memory continue to expand.

[0005] A NAND flash memory is a common type of flash memory device, so called for the logical form in which the basic memory cell configuration is arranged. Typically, the array of memory cells for NAND flash memory is arranged such that the control gate of each memory cell of a row of the array is connected together to form an access line, such as a word line. Columns of the array include strings (often termed NAND strings) of memory cells connected together in series between a pair of select gates, e.g., a source select transistor and a drain select transistor. Each source select transistor might be connected to a source, while each drain select transistor might be connected to a data line, such as column bit line. Variations using more than one select gate between a string of memory cells and the source, and/or between the string of memory cells and the data line, are known.

[0006] In programming memory, memory cells might be programmed as what are often termed single-level cells (SLC). SLC might use a single memory cell to represent one digit (e.g., one bit) of data. For example, in SLC, a Vt of 2.5V or higher might indicate a programmed memory cell (e.g., representing a logical 0) while a Vt of −0.5V or lower might indicate an erased memory cell (e.g., representing a logical 1). Such memory might achieve higher levels of storage capacity by

including multi-level cells (MLC), triple-level cells (TLC), quad-level cells (QLC), etc., or combinations thereof in which the memory cell has multiple levels that enable more digits of data to be stored in each memory cell. For example, MLC might be configured to store two digits of data per memory cell represented by four Vt ranges, TLC might be configured to store three digits of data per memory cell represented by eight Vt ranges, QLC might be configured to store four digits of data per memory cell represented by sixteen Vt ranges, and so on.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

[0007] FIG. **1** is a simplified block diagram of a memory in communication with a processor as part of an electronic system, according to an embodiment.

[0008] FIGS. **2**A-**2**C are schematics of portions of an array of memory cells as could be used in a memory of the type described with reference to FIG. **1**.

[0009] FIGS. **3**A-**3**B are conceptual depictions of threshold voltage distributions of a plurality of memory cells.

[0010] FIGS. **4**A-**4**B are schematics of portions of a page buffer circuit as could be used in a memory of the type described with reference to FIG. **1**.

[0011] FIG. **5**A is a timing diagram depicting voltage levels of data lines and a selected access line for a Single SSPC programming operation.

[0012] FIG. **5**B conceptually depicts the threshold voltage changes for different groupings of memory cells of the programming operation of FIG. **5**A.

[0013] FIG. **6**A is a timing diagram depicting voltage levels of data lines and a selected access line for a Dual SSPC programming operation.

[0014] FIG. **6**B conceptually depicts the threshold voltage changes for different groupings of memory cells of the programming operation of FIG. **6**A.

[0015] FIG. **7**A is a timing diagram depicting voltage levels of data lines and a selected access line for a programming operation in accordance with an embodiment.

[0016] FIG. **7**B conceptually depicts the threshold voltage changes for different groupings of memory cells of the programming operation of FIG. **7**A.

[0017] FIG. **8** shows a plot of an access line voltage versus time of a programming operation in accordance with embodiments.

[0018] FIG. **9** is a conceptual depiction of a verify phase of the programming operation of FIG. **8**.

[0019] FIG. **10** is a timing diagram generally depicting voltage levels of various nodes of a page buffer circuit at various stages of a verify phase of a programming operation in accordance with an embodiment.

[0020] FIGS. **11**A-**11**B depict alternate examples of suitable source-follower transistors for use with embodiments.

[0021] FIGS. **12**A-**12**B depict conceptual relationships between control gate voltages of a source-follower transistor, and voltage levels of a source of the transistor for a particular voltage level applied to its drain.

[0022] FIG. **13** is a flowchart of a method of operating a memory in accordance with an embodiment.

[0023] FIG. **14** is a flowchart of a method of operating a memory in accordance with another embodiment.

[0024] FIG. **15** is a flowchart of a method of operating a memory in accordance with a further embodiment.

[0025] FIGS. **16**A-**16**B are a flowchart of a method of operating a memory in accordance with a still further embodiment.

[0026] FIGS. **17**A-**17**C are a flowchart of a method of operating a memory in accordance with a still further embodiment.
[0027] FIG. **18** is a schematic of portions of an array of memory cells in accordance with additional embodiments.
DETAILED DESCRIPTION
[0028] In the following detailed description, reference is made to the accompanying drawings that form a part hereof, and in which is shown, by way of illustration, specific embodiments. In the drawings, like reference numerals describe substantially similar components throughout the several views. Other embodiments might be utilized and structural, logical and electrical changes might be made without departing from the scope of the present disclosure. The following detailed description is, therefore, not to be taken in a limiting sense.
[0029] The term “semiconductor” used herein can refer to, for example, a layer of material, a wafer, or a substrate, and includes any base semiconductor structure. “Semiconductor” is to be understood as including silicon-on-sapphire (SOS) technology, silicon-on-insulator (SOI) technology, thin film transistor (TFT) technology, doped and undoped semiconductors, epitaxial layers of a silicon supported by a base semiconductor structure, as well as other semiconductor structures well known to one skilled in the art. Furthermore, when reference is made to a semiconductor in the following description, previous process steps might have been utilized to form regions/junctions in the base semiconductor structure, and the term semiconductor can include the underlying layers containing such regions/junctions.
[0030] The term “conductive” as used herein, as well as its various related forms, e.g., conduct, conductively, conducting, conduction, conductivity, etc., refers to electrically conductive unless otherwise apparent from the context. Similarly, the term “connecting” as used herein, as well as its various related forms, e.g., connect, connected, connection, etc., refers to electrically connecting by an electrically conductive path unless otherwise apparent from the context.
[0031] It is recognized herein that even where values might be intended to be equal, variabilities and accuracies of industrial processing and operation might lead to differences from their intended values. These variabilities and accuracies will generally be dependent upon the technology utilized in fabrication and operation of the integrated circuit device. As such, if values are intended to be equal, those values are deemed to be equal regardless of their resulting values.
[0032] Programming in memories is typically accomplished by applying one or more programming pulses, separated by verify pulses, to program each memory cell of a selected group of memory cells to a respective target data state (which might be an interim or final data state). With such a scheme, the programming pulses are applied to access lines, such as those typically referred to as word lines, for selected memory cells. After each programming pulse, one or more verify voltage levels are typically used to verify the programming of the selected memory cells. Programming typically uses many programming pulses in an incremental step pulse programming (ISPP) scheme, where each programming pulse is a single-level pulse that moves the memory cell threshold voltage by some amount.
[0033] The programming pulses might be applied to a selected access line (e.g., word line) and thus to the control gates of the row of memory cells connected to the selected access line (e.g., having their control gates connected to the selected access line). Typical programming pulses might start at or near 13V and tend to increase in magnitude for each subsequent programming pulse application. While the program potential (e.g., voltage level of the programming pulse) is applied to the selected access line, an enable voltage, such as a reference potential (e.g., 0V), might be applied to the channels of memory cells selected for programming, i.e., those memory cells for which the programming operation is intended to shift their data state to some higher level. This might result in a charge transfer from the channel to the charge storage structures of these selected memory cells. For example, floating gates are typically charged through direct injection or Fowler-Nordheim tunneling of electrons from the channel to the floating gate, resulting in an increased

threshold voltage in a programmed state.

[0034] An inhibit voltage (e.g., Vcc) is typically applied to data lines which are selectively connected to a NAND string containing a memory cell that is connected to the selected access line and is not selected for, or is no longer selected for, programming. In addition to data lines selectively connected to memory cells already at their target data state, these unselected data lines might further include data lines that are not addressed by the programming operation. For example, a logical page of data might correspond to memory cells connected to a particular access line and selectively connected to some particular subset of the data lines (e.g., every other data line), such that the remaining subset of data lines would be unselected for the programming operation and thus inhibited.

[0035] Between the application of one or more programming pulses, a verify phase of the programming operation is typically performed to check each selected memory cell to determine if it has reached its target data state. If a selected memory cell has reached its target data state, it might be inhibited from further programming if there remain other selected memory cells still requiring additional programming pulses to reach their target data states. Following a verify phase, an additional programming pulse might be applied if there are memory cells that have not completed programming. This process of applying a programming pulse followed by verification (e.g., a programming phase and a verify, or sensing, phase of a programming operation) typically continues until all the selected memory cells have reached their target data states. If a particular number of programming pulses (e.g., maximum number) have been applied, or a particular voltage level of a programming pulse (e.g., maximum voltage level) has been reached, and one or more selected memory cells still have not completed programming, those memory cells might be marked as defective, for example.

[0036] The use of different voltage levels on data lines to be enabled for programming might occur in programming schemes known as selective slow programming convergence (SSPC), where memory cells nearer to their respective target data states are programmed more slowly (e.g., partially enabled for programming) compared to memory cells farther from their respective target data states (e.g., fully enabled for programming) while receiving a same voltage level at their respective control gates. SSPC programming schemes can facilitate more narrow distributions of threshold voltages defining each data state over more traditional programming schemes that rely on memory cells being either fully enabled or inhibited from programming. By narrowing the threshold voltage distributions, and thus providing more dead space, or margin, between adjacent threshold voltage distributions, accuracy of determining data states of memory cells might be improved and/or memory density (e.g., number of digits of data per memory cell) might be increased.

[0037] Although SSPC programming schemes can provide for tighter threshold voltage distributions over more traditional programming schemes, that benefit typically comes with a cost. In particular, memory cells subject to the programming operation must generally be apportioned to different subsets of memory cells for each programming pulse, e.g., one subset of memory cells to be inhibited from programming, one subset of memory cells to be enabled (e.g., fully enabled) for programming, and one subset of memory cells for each level of partial enablement of programming. Each subset of memory cells might correspond to a respective, mutually exclusive, range of threshold voltages. The threshold voltage for each memory cell subject to the programming operation must generally be determined or estimated in order to apportion it to the proper subset of memory cells. This can add time and/or complexity to the verify phase of the programming operation.

[0038] Various embodiments seek to facilitate further narrowing of threshold voltage distributions over typical SSPC programming schemes, while mitigating a need to apportion memory cells for each level of partial enablement of programming. Such embodiments might provide a data line voltage level during a subsequent programming pulse that is inversely related to its corresponding

NAND string current level (e.g., I.sub.string) during a verify phase of the programming operation (e.g., an immediately prior verify phase of the programming operation). Consider the example of eight NAND strings each having a memory cell selected for programming during a programming operation, and exhibiting I.sub.string values of I.sub.0, I.sub.1, I.sub.2, I.sub.3, I.sub.4, I.sub.5, I.sub.6, and I.sub.7 during a verify phase of the programming operation, where I.sub.0<I.sub.1<I.sub.2<I.sub.3<I.sub.4<I.sub.5<I.sub.6<I.sub.7. During a subsequent programming pulse, their corresponding data lines might receive voltage levels of V.sub.0, V.sub.1, V.sub.2, V.sub.3, V.sub.4, V.sub.5, V.sub.6, and V.sub.7, respectively, where V.sub.0>V.sub.1>V.sub.2>V.sub.3>V.sub.4>V.sub.5>V.sub.6>V.sub.7.

[0039] Various embodiments might capture a retained voltage level of a node of a page buffer circuit following or during a verify phase of the programming operation. During the verify phase of the programming operation, the node might be precharged, and then selectively discharged through a data line responsive to a level of activation of a selected memory cell of a programming operation. As such, a memory cell having a higher threshold voltage, e.g., lower I.sub.string in response to a given control gate voltage level, might be expected to result in a higher retained voltage level at the node than a memory cell having a lower threshold voltage, e.g., higher I.sub.string in response to the given control gate voltage level. The remaining voltage level of the node might subsequently be used as a control voltage of a source-follower to generate a data line voltage level for a subsequent programming operation. In this manner, memory cells closer to their target threshold voltage might be expected to receive a higher data line voltage, e.g., lower level of partial enablement, and memory cells farther from their target threshold voltage might be expected to receive a lower data line voltage, e.g., higher level of partial enablement.

[0040] FIG. **1** is a simplified block diagram of a first apparatus, in the form of a memory (e.g., memory device) **100**, in communication with a second apparatus, in the form of a processor **130**, as part of a third apparatus, in the form of an electronic system, according to an embodiment. Some examples of electronic systems include personal computers, personal digital assistants (PDAs), digital cameras, digital media players, digital recorders, games, appliances, vehicles, wireless devices, mobile telephones and the like. The processor **130**, e.g., a controller external to the memory device **100**, might be a memory controller or other external host device.

[0041] Memory device **100** includes an array of memory cells **104** that might be logically arranged in rows and columns. Memory cells of a logical row are typically connected to the same access line (commonly referred to as a word line) while memory cells of a logical column are typically selectively connected to the same data line (commonly referred to as a bit line). A single access line might be associated with more than one logical row of memory cells and a single data line might be associated with more than one logical column. Memory cells (not shown in FIG. **1**) of at least a portion of array of memory cells **104** are capable of being programmed to one of at least two target data states.

[0042] Row decode circuitry **108** and column decode circuitry **110** are provided to decode address signals. Address signals are received and decoded to access the array of memory cells **104**. Memory device **100** also includes input/output (I/O) control circuitry **112** to manage input of commands, addresses and data to the memory device **100** as well as output of data and status information from the memory device **100**. An address register **114** is in communication with I/O control circuitry **112**, and with row decode circuitry **108** and column decode circuitry **110**, to latch the address signals prior to decoding. A command register **124** is in communication with I/O control circuitry **112** and control logic **116** to latch incoming commands.

[0043] A controller (e.g., the control logic **116** internal to the memory device **100**) controls access to the array of memory cells **104** in response to the commands and might generate status information for the external processor **130**, i.e., control logic **116** is configured to perform array operations (e.g., sensing operations [which might include read operations and verify phases of programming operations], programming operations and/or erase operations) on the array of

memory cells **104**. The control logic **116** is in communication with row decode circuitry **108** and column decode circuitry **110** to control the row decode circuitry **108** and column decode circuitry **110** in response to the addresses. The control logic **116** might include instruction registers **128** which might represent computer-usable memory for storing computer-readable instructions. For some embodiments, the instruction registers **128** might represent firmware. Alternatively, the instruction registers **128** might represent a grouping of memory cells, e.g., reserved block(s) of memory cells, of the array of memory cells **104**. The control logic **116** might be configured to cause the memory, e.g., to cause relevant components of the memory, to perform methods according to various embodiments, e.g., through execution of computer-readable instructions stored to the instruction registers **128**.

[0044] Control logic **116** might also be in communication with a cache register **118**. Cache register **118** latches data, either incoming or outgoing, as directed by control logic **116** to temporarily store data while the array of memory cells **104** is busy writing or reading, respectively, other data. During a programming operation (e.g., write operation), data might be passed from the cache register **118** to the data register **120** for transfer to the array of memory cells **104**, then new data might be latched in the cache register **118** from the I/O control circuitry **112**. During a read operation, data might be passed from the cache register **118** to the I/O control circuitry **112** for output to the external processor **130**, then new data might be passed from the data register **120** to the cache register **118**. The cache register **118** and/or the data register **120** might form (e.g., might form a portion of) a page buffer of the memory device **100**. A data register **120** might further include page buffer circuits (not shown in FIG. **1**) to sense a data state of a memory cell of the array of memory cells **104**, e.g., by sensing a state of a data line connected to that memory cell. A status register **122** might be in communication with I/O control circuitry **112** and control logic **116** to latch the status information for output to the processor **130**.

[0045] A trim register **127** might be in communication with the control logic **116**. The trim register **127** might represent a volatile memory, latches, or other storage location, e.g., volatile or non-volatile. For some embodiments, the trim register **127** might represent a portion of the array of memory cells **104**. Trims might be used by the memory to set values used by an array operation, e.g., voltage levels, timing characteristics, etc., or might be used to selectively activate or deactivate features of the memory.

[0046] Memory device **100** receives control signals at control logic **116** from processor **130** over a control link **132**. The control signals might include a chip enable CE #, a command latch enable CLE, an address latch enable ALE, a write enable WE #, a read enable RE #, and a write protect WP #. Additional or alternative control signals (not shown) might be further received over control link **132** depending upon the nature of the memory device **100**. Memory device **100** receives command signals (which represent commands), address signals (which represent addresses), and data signals (which represent data) from processor **130** over a multiplexed input/output (I/O) bus **134** and outputs data to processor **130** over I/O bus **134**.

[0047] For example, the commands might be received over input/output (I/O) pins [7:0] of I/O bus **134** at I/O control circuitry **112** and might then be written into command register **124**. The addresses might be received over input/output (I/O) pins [7:0] of I/O bus **134** at I/O control circuitry **112** and might then be written into address register **114**. The data might be received over input/output (I/O) pins [7:0] for an 8-bit device or input/output (I/O) pins [15:0] for a 16-bit device at I/O control circuitry **112** and then might be written into cache register **118**. The data might be subsequently written into data register **120** for programming the array of memory cells **104**. Data might also be output over input/output (I/O) pins [7:0] for an 8-bit device or input/output (I/O) pins [15:0] for a 16-bit device. Although reference might be made to I/O pins, they might include any conductive nodes providing for electrical connection to the memory device **100** by an external device (e.g., processor **130**), such as conductive pads or conductive bumps as are commonly used.

[0048] It will be appreciated by those skilled in the art that additional circuitry and signals can be

provided, and that the memory device **100** of FIG. **1** has been simplified. It should be recognized that the functionality of the various block components described with reference to FIG. **1** might not necessarily be segregated to distinct components or component portions of an integrated circuit device. For example, a single component or component portion of an integrated circuit device could be adapted to perform the functionality of more than one block component of FIG. **1**. Alternatively, one or more components or component portions of an integrated circuit device could be combined to perform the functionality of a single block component of FIG. **1**.

[0049] Additionally, while specific I/O pins are described in accordance with popular conventions for receipt and output of the various signals, it is noted that other combinations or numbers of I/O pins (or other I/O node structures) might be used in the various embodiments.

[0050] FIG. **2**A is a schematic of a portion of an array of memory cells **200**A, such as a NAND memory array, as could be used in a memory of the type described with reference to FIG. **1**, e.g., as a portion of array of memory cells **104**. Memory array **200**A includes access lines (e.g., word lines) **202**.sub.0 to **202**.sub.N, and data lines (e.g., bit lines) **204**.sub.0 to **204**.sub.M. The access lines **202** might be connected to global access lines (e.g., global word lines), not shown in FIG. **2**A, in a many-to-one relationship. For some embodiments, memory array **200**A might be formed over a semiconductor that, for example, might be conductively doped to have a conductivity type, such as a p-type conductivity, e.g., to form a p-well, or an n-type conductivity, e.g., to form an n-well.

[0051] Memory array **200**A might be arranged in rows (each corresponding to an access line **202**) and columns (each corresponding to a data line **204**). Each column might include a string of series-connected memory cells (e.g., non-volatile memory cells), such as one of NAND strings **206**.sub.0 to **206**.sub.M. Each NAND string **206** might be connected (e.g., selectively connected) to a common source (SRC) **216** and might include memory cells **208**.sub.0 to **208**.sub.N. The memory cells **208** might represent non-volatile memory cells for storage of data. The memory cells **208**.sub.0 to **208**.sub.N might include memory cells intended for storage of data, and might further include other memory cells not intended for storage of data, e.g., dummy memory cells. Dummy memory cells are typically not accessible to a user of the memory, and are instead typically incorporated into the string of series-connected memory cells for operational advantages that are well understood.

[0052] The memory cells **208** of each NAND string **206** might be connected in series between a select gate **210** (e.g., a field-effect transistor), such as one of the select gates **210**.sub.0 to **210**.sub.M (e.g., that might be source select transistors, commonly referred to as select gate source), and a select gate **212** (e.g., a field-effect transistor), such as one of the select gates **212**.sub.0 to **212**.sub.M (e.g., that might be drain select transistors, commonly referred to as select gate drain). Select gates **210**.sub.0 to **210**.sub.M might be commonly connected to a select line **214**, such as a source select line (SGS), and select gates **212**.sub.0 to **212**.sub.M might be commonly connected to a select line **215**, such as a drain select line (SGD). Although depicted as traditional field-effect transistors, the select gates **210** and **212** might utilize a structure similar to (e.g., the same as) the memory cells **208**. The select gates **210** and **212** might represent a plurality of select gates connected in series, with each select gate in series configured to receive a same or independent control signal. In addition, for embodiments utilizing a plurality of select gates connected in series, such select gates might be configured to have the same or different threshold voltages. For example, where gate-induced drain leakage current (GIDL) is desired for programming operations, one or more select gates of the series-connected select gates might have a different (e.g., lower) threshold voltage than one or more other select gates of the series-connected select gates.

[0053] A source of each select gate **210** might be connected to common source **216**. The drain of each select gate **210** might be connected to a memory cell **208**.sub.0 of the corresponding NAND string **206**. For example, the drain of select gate **210**.sub.0 might be connected to memory cell **208**.sub.0 of the corresponding NAND string **206**.sub.0. Therefore, each select gate **210** might be

configured to selectively connect a corresponding NAND string **206** to common source **216**. A control gate of each select gate **210** might be connected to select line **214**.
[0054] The drain of each select gate **212** might be connected to the data line **204** for the corresponding NAND string **206**. For example, the drain of select gate **212**.sub.0 might be connected to the data line **204**.sub.0 for the corresponding NAND string **206**.sub.0. The source of each select gate **212** might be connected to a memory cell **208**.sub.N of the corresponding NAND string **206**. For example, the source of select gate **212**.sub.0 might be connected to memory cell **208**.sub.N of the corresponding NAND string **206**.sub.0. Therefore, each select gate **212** might be configured to selectively connect a corresponding NAND string **206** to the corresponding data line **204**. A control gate of each select gate **212** might be connected to select line **215**.
[0055] The memory array in FIG. **2**A might be a quasi-two-dimensional memory array and might have a generally planar structure, e.g., where the common source **216**, NAND strings **206** and data lines **204** extend in substantially parallel planes. Alternatively, the memory array in FIG. **2**A might be a three-dimensional memory array, e.g., where NAND strings **206** might extend substantially perpendicular to a plane containing the common source **216** and to a plane containing the data lines **204** that might be substantially parallel to the plane containing the common source **216**.
[0056] Typical construction of memory cells **208** includes a data-storage structure **234** (e.g., a floating gate, charge trap, or other structure configured to store charge) that can determine a data state of the memory cell (e.g., through changes in threshold voltage), and a control gate **236**, as shown in FIG. **2**A. The data-storage structure **234** might include both conductive and dielectric structures while the control gate **236** is generally formed of one or more conductive materials. In some cases, memory cells **208** might further have a defined source/drain (e.g., source) **230** and a defined source/drain (e.g., drain) **232**. Memory cells **208** have their control gates **236** connected to (and in some cases form) an access line **202**.
[0057] A column of the memory cells **208** might be a NAND string **206** or a plurality of NAND strings **206** selectively connected to a given data line **204**. A row of the memory cells **208** might be memory cells **208** commonly connected to a given access line **202**. A row of memory cells **208** can, but need not, include all memory cells **208** commonly connected to a given access line **202**. Rows of memory cells **208** might often be divided into one or more groups of physical pages of memory cells **208**, and physical pages of memory cells **208** often include every other memory cell **208** commonly connected to a given access line **202**. For example, memory cells **208** commonly connected to access line **202**.sub.N and selectively connected to even data lines **204** (e.g., data lines **204**.sub.0, **204**.sub.2, **204**.sub.4, etc.) might be one physical page of memory cells **208** (e.g., even memory cells) while memory cells **208** commonly connected to access line **202**.sub.N and selectively connected to odd data lines **204** (e.g., data lines **204**.sub.1, **204**.sub.3, **204**.sub.5, etc.) might be another physical page of memory cells **208** (e.g., odd memory cells). Although data lines **204**.sub.3-**204**.sub.5 are not explicitly depicted in FIG. **2**A, it is apparent from the figure that the data lines **204** of the array of memory cells **200**A might be numbered consecutively from data line **204**.sub.0 to data line **204**.sub.M. Other groupings of memory cells **208** commonly connected to a given access line **202** might also define a physical page of memory cells **208**. For certain memory devices, all memory cells commonly connected to a given access line might be deemed a physical page of memory cells. The portion of a physical page of memory cells (which, in some embodiments, could still be the entire row) that is read during a single read operation or programmed during a single programming operation (e.g., an upper or lower page of memory cells) might be deemed a logical page of memory cells. A block of memory cells might include those memory cells that are configured to be erased together, such as all memory cells connected to access lines **202**.sub.0-**202**.sub.N (e.g., all NAND strings **206** sharing common access lines **202**). Unless expressly distinguished, a reference to a page of memory cells herein refers to the memory cells of a logical page of memory cells.
[0058] Although the example of FIG. **2**A is discussed in conjunction with NAND flash, the

embodiments and concepts described herein are not limited to a particular array architecture or structure, and can include other structures (e.g., SONOS or other data storage structure configured to store charge) and other architectures (e.g., AND arrays, NOR arrays, etc.).

[0059] FIG. **2**B is another schematic of a portion of an array of memory cells **200**B as could be used in a memory of the type described with reference to FIG. **1**, e.g., as a portion of array of memory cells **104**. Like numbered elements in FIG. **2**B correspond to the description as provided with respect to FIG. **2**A. FIG. **2**B provides additional detail of one example of a three-dimensional NAND memory array structure. The three-dimensional NAND memory array **200**B might incorporate vertical structures which might include semiconductor pillars, which might be solid or hollow, where a portion of a pillar might act as a channel region of the memory cells of NAND strings **206**, e.g., a region through which current might flow when a memory cell, e.g., a field-effect transistor, is activated. The NAND strings **206** might be each selectively connected to a data line **204**.sub.0-**204**.sub.M by a select transistor **212** (e.g., that might be drain select transistors, commonly referred to as select gate drain) and to a common source **216** by a select transistor **210** (e.g., that might be source select transistors, commonly referred to as select gate source). Multiple NAND strings **206** might be selectively connected to the same data line **204**. Subsets of NAND strings **206** can be connected to their respective data lines **204** by biasing the select lines **215**.sub.0-**215**.sub.K to selectively activate particular select transistors **212** each between a NAND string **206** and a data line **204**. The select transistors **210** can be activated by biasing the select line **214**. Each access line **202** might be connected to multiple rows of memory cells of the memory array **200**B. Rows of memory cells that are commonly connected to each other by a particular access line **202** might collectively be referred to as tiers.

[0060] The three-dimensional NAND memory array **200**B might be formed over peripheral circuitry **226**. The peripheral circuitry **226** might represent a variety of circuitry for accessing the memory array **200**B. The peripheral circuitry **226** might include complementary circuit elements. For example, the peripheral circuitry **226** might include both n-channel region and p-channel region transistors formed on a same semiconductor substrate, a process commonly referred to as CMOS, or complementary metal-oxide-semiconductors. Although CMOS often no longer utilizes a strict metal-oxide-semiconductor construction due to advancements in integrated circuit fabrication and design, the CMOS designation remains as a matter of convenience.

[0061] FIG. **2**C is a further schematic of a portion of an array of memory cells **200**C as could be used in a memory of the type described with reference to FIG. **1**, e.g., as a portion of array of memory cells **104**. Like numbered elements in FIG. **2**C correspond to the description as provided with respect to FIG. **2**A. Array of memory cells **200**C might include strings of series-connected memory cells (e.g., NAND strings) **206**, access (e.g., word) lines **202**, data (e.g., bit) lines **204**, select lines **214** (e.g., source select lines), select lines **215** (e.g., drain select lines) and source **216** as depicted in FIG. **2**A. A portion of the array of memory cells **200**A might be a portion of the array of memory cells **200**C, for example. FIG. **2**C depicts groupings of NAND strings **206** into blocks of memory cells **250**, e.g., blocks of memory cells **250**.sub.0-**250**.sub.L. Blocks of memory cells **250** might be groupings of memory cells **208** that might be erased together in a single erase operation, sometimes referred to as erase blocks. Each block of memory cells **250** might represent those NAND strings **206** commonly associated with a single select line **215**, e.g., select line **215**.sub.0. The source **216** for the block of memory cells **250**.sub.0 might be a same source as the source **216** for the block of memory cells **250**.sub.L. For example, each block of memory cells **250**.sub.0-**250**.sub.L might be commonly selectively connected to the source **216**. Access lines **202** and select lines **214** and **215** of one block of memory cells **250** might have no direct connection to access lines **202** and select lines **214** and **215**, respectively, of any other block of memory cells **250** of the blocks of memory cells **250**.sub.0-**250**.sub.L.

[0062] The data lines **204**.sub.0-**204**.sub.M might be connected (e.g., selectively connected) to a buffer portion **240**, which might be a portion of a page buffer of the memory. The buffer portion

240 might correspond to a memory plane (e.g., the set of blocks of memory cells **250**.sub.0-**250**.sub.L). The buffer portion **240** might include page buffer circuits (not shown in FIG. **2**C) for programming data values to, and sensing data values from, memory cells selectively connected to respective data lines **204**. The buffer portion **240** might include a portion of the data register **120** and a portion of the cache register **118** corresponding to the blocks of memory cells **250**.sub.0-**250**.sub.L.

[0063] FIG. **3**A is a conceptual depiction of threshold voltage ranges of a plurality of memory cells. FIG. **3**B illustrates an example of threshold voltage ranges and their distributions for a population of a eight-level memory cells, often referred to as TLC memory cells. For example, such a memory cell might be programmed to a threshold voltage (Vt) that falls within one of eight different threshold voltage ranges **330**.sub.0-**330**.sub.7, each being used to represent a data state corresponding to a bit pattern of three bits. The threshold voltage range **330**.sub.0 typically has a greater width than the remaining threshold voltage ranges **330**.sub.1-**330**.sub.7 as memory cells are generally all placed in the data state corresponding to the threshold voltage range **330**.sub.0, then subsets of those memory cells are subsequently programmed to have threshold voltages in one of the threshold voltage ranges **330**.sub.1-**330**.sub.7. As programming operations are generally more incrementally controlled than erase operations, these threshold voltage ranges **330**.sub.1-**330**.sub.7 may tend to have tighter distributions.

[0064] The threshold voltage ranges **330**.sub.0, **330**.sub.1, **330**.sub.2, **330**.sub.3, **330**.sub.4, **330**.sub.5, **330**.sub.6, and **330**.sub.7 might each represent a respective data state, e.g., L0, L1, L2, L3, L4, L5, L6, and L7, respectively. As an example, if the threshold voltage of a memory cell is within the first of the eight threshold voltage ranges **330**.sub.0, the memory cell in this case may be storing a data state L0 having a data value of logical ‘111’ and is typically referred to as the erased state of the memory cell. If the threshold voltage is within the second of the eight threshold voltage ranges **330**.sub.1, the memory cell in this case may be storing a data state L1 having a data value of logical ‘011’. If the threshold voltage is within the third of the eight threshold voltage ranges **330**.sub.2, the memory cell in this case may be storing a data state L2 having a data value of logical ‘001’, and so on. Table 1 provides one possible correspondence between the data states and their corresponding logical data values. Other assignments of data states to logical data values are known. Memory cells remaining in the lowest data state (e.g., the erased state or L0 data state), as used herein, will be deemed to be programmed to the lowest data state. The information of Table 1 might be contained within the trim register **127**, for example.

TABLE-US-00001 TABLE 1 Data State Logical Data Value L0 111 L1 011 L2 001 L3 101 L4 100 L5 000 L6 010 L7 110

[0065] FIG. **3**B is another conceptual depiction of threshold voltage ranges of a plurality of memory cells. FIG. **3**B illustrates an example of threshold voltage ranges and their distributions for a population of a sixteen-level memory cells, often referred to as QLC memory cells. For example, such a memory cell might be programmed to a threshold voltage (Vt) that falls within one of sixteen different threshold voltage ranges **330**.sub.0-**330**.sub.15, each being used to represent a data state corresponding to a bit pattern of four bits. The threshold voltage range **330**.sub.0 typically has a greater width than the remaining threshold voltage ranges **330**.sub.1-**330**.sub.15 as memory cells are generally all placed in the data state corresponding to the threshold voltage range **330**.sub.0, then subsets of those memory cells are subsequently programmed to have threshold voltages in one of the threshold voltage ranges **330**.sub.1-**330**.sub.15. As programming operations are generally more incrementally controlled than erase operations, these threshold voltage ranges **330**.sub.1-**330**.sub.15 may tend to have tighter distributions.

[0066] The threshold voltage ranges **330**.sub.0, **330**.sub.1, **330**.sub.2, **330**.sub.3, **330**.sub.4, **330**.sub.5, **330**.sub.6, **330**.sub.7, **330**.sub.8, **330**.sub.9, **330**.sub.10, **330**.sub.11, **330**.sub.12, **330**.sub.13, **330**.sub.14 and **330**.sub.15 might each represent a respective data state, e.g., L0, L1, L2, L3, L4, L5, L6, L7, L8, L9, L10, L11, L12, L13, L14 and L15, respectively. As an example, if

the threshold voltage of a memory cell is within the first of the sixteen threshold voltage ranges **330**.sub.0, the memory cell in this case may be storing a data state L0 having a data value of logical '1111' and is typically referred to as the erased state of the memory cell. If the threshold voltage is within the second of the sixteen threshold voltage ranges **330**.sub.1, the memory cell in this case may be storing a data state L1 having a data value of logical '0111'. If the threshold voltage is within the third of the sixteen threshold voltage ranges **330**.sub.2, the memory cell in this case may be storing a data state L2 having a data value of logical '0011', and so on. Table 2 provides one possible correspondence between the data states and their corresponding logical data values. Other assignments of data states to logical data values are known. Memory cells remaining in the lowest data state (e.g., the erased state or L0 data state), as used herein, will be deemed to be programmed to the lowest data state. The information of Table 2 might be contained within the trim register **127**, for example.

TABLE-US-00002 TABLE 2 Data State Logical Data Value L0 1111 L1 0111 L2 0011 L3 1011 L4 1001 L5 0001 L6 0101 L7 1101 L8 1100 L9 0100 L10 0000 L11 1000 L12 1010 L13 0010 L14 0110 L15 1110

[0067] As memory cells are reduced in size, their associated data storage structures generally become smaller. In addition, as more levels of data states are stored to memory cells, differentiation between data states may become more difficult.

[0068] FIGS. **4**A-**4**B are schematics of portions of a page buffer circuit **400** as could be used in a memory of the type described with reference to FIG. **1**. Page buffer circuit **400** might be part of buffer portion **240** of FIG. **2**C. Page buffer circuit **400** might be connected (e.g., selectively connected) to a NAND string **206** through a data line **204**.

[0069] Page buffer circuit **400** might include transistors **401**, **403**, **405**, **407**, **409**, **411**, **413**, **415**, **419**, **421**, **433**, **435**, **438**, **439**, **441**, **447**, **449**, **451**, **453**, and **455**. The page buffer circuit **400** might further include a sense capacitor **417**, a sense amplifier latch **431**, and a data latch **462**. Transistor **413** might be a p-type field-effect transistor (pFET), while transistors **401**, **403**, **405**, **407**, **409**, **411**, **415**, **419**, **421**, **433**, **435**, **438**, **439**, **441**, **447**, **449**, **451**, **453**, and **455** might be n-type field-effect transistors (nFETs). Sense amplifier latch **431** might include inverters **427** and **429** and transistors **423** and **425** (e.g., nFETs). Data latch (e.g., PDC2) **462** might include inverters **458** and **460** and transistors **443** and **445** (e.g., nFETs).

[0070] The data line **204** might be connected to a first source/drain of transistor **401** and a first source/drain of transistor **403**. The control gate of transistor **403** might be connected to a src_gate control signal node **404**. The second source/drain of transistor **403** might be connected to the common source **216**. The control gate of transistor **401** might be connected to a dw_gate control signal node **402**. The second source/drain of transistor **401** might be connected to a first source/drain of transistor **405**.

[0071] The control gate of transistor **405** might be connected to a blclamp control signal node **406**. The second source/drain of transistor **405** might be connected to a first source/drain of transistor **407**, a first source/drain of transistor **409**, and a first source/drain of transistor **411**. The control gate of transistor **407** might be connected to a blclamp2 control signal node **408**. The second source/drain of transistor **407** might be connected to a first source/drain of transistor **413**. The control gate of transistor **413** might be connected to a first source/drain of transistor **453** and the control gate of transistor **415**. The control gate of transistor **453** might be connected to a sab_bl_pre control signal node **454**. The second source/drain of transistor **453** might be connected to the input of inverter **427**, the output of inverter **429**, and a first source/drain of transistor **423**. The second source/drain of transistor **413** might be connected to a voltage node (e.g., vreg2) **414**. The control gate of transistor **409** might be connected to an en_data control signal node **410**. The second source/drain of transistor **409** might be connected to a first source/drain of transistor **415**. The second source/drain of transistor **415** might be connected to a voltage node (e.g., vreg0) **416**.

[0072] The control gate of transistor **411** might be connected to a tc_iso control signal node **412**.

The second source/drain of transistor **411** might be connected to one side (e.g., a first electrode) of sense capacitor **417**, a first source/drain of transistor **419**, and the control gate of transistor **451** through a tc signal node **432**. The other side (e.g., a second electrode) of sense capacitor **417** might be connected to a sense capacitor bias node (e.g., boost node) **418**. The control gate of transistor **419** might be connected to a blc1 control signal node **420**. The second source/drain of transistor **419** might be connected to a first source/drain of transistor **421**, the second source/drain of transistor **423**, a first source/drain of transistor **425**, a first source/drain of transistor **433**, a first source/drain of transistor **435**, a first source/drain of transistor **437**, a first source/drain of transistor **439**, and a first source/drain of transistor **441**.

[0073] The control gate of transistor **433** might be connected to a en_sspc2 control signal node **434**. The second source/drain of transistor **433** might be connected to a first source/drain of transistor **447**. The second source/drain of transistor **447** might be connected to a voltage node (e.g., vcc) **448**. The control gate of transistor **435** might be connected to a dl_set control signal node **436**. The second source/drain of transistor **435** might be connected to a first source/drain of transistor **449**. The control gate of transistor **449** might be connected to a d_latch control signal node **450**. The second source/drain of transistor **449** might be connected to the control gate of transistor **447**.

[0074] The control gate of transistor **421** might be connected to a sen control signal node **422**. The second source/drain of transistor **421** might be connected to a first source/drain of transistor **451**. The second source/drain of transistor **451** might be connected to a source bias node (e.g., src_gnd) **452**. The transistor **451** might be referred to as a sense transistor.

[0075] The control gate of transistor **423** of sense amplifier latch **431** might be connected to a drst_sa control signal node **424**. The control gate of transistor **425** might be connected to a dst_sa control signal node **426**. The second source/drain of transistor **425** might be connected to the output of inverter **427** and to the input of inverter **429**. A control input of inverter **427** might be connected to a sen_sab control signal node **428**. A control input of inverter **429** might be connected to a lat_sab control signal node **430**.

[0076] The control gate of transistor **437** might be connected to a tccint_dis control signal node **438**. The second source/drain of transistor **437** might be connected to a first source/drain of transistor **455** and to a voltage node (e.g., vprech) **457**. The control gate of transistor **439** might be connected to the second source/drain of transistor **441**, a first source/drain of transistor **443**, and a first source/drain of transistor **445**. The control gate of transistor **441** might be connected to a blc2 control signal node **442**. The control gate of transistor **455** might be connected to a en_sa control signal node **456**. The second source/drain of transistor **455** might be connected to the second source/drain of transistor **439**.

[0077] The control gate of transistor **443** of data latch **462** might be connected to a drst2 control signal node **444**. The control gate of transistor **445** might be connected to a dst2 control signal node **446**. The second source/drain of transistor **443** might be connected to the output of inverter **460** and to the input of inverter **458**. The second source/drain of transistor **445** might be connected to the output of inverter **458** and to the input of inverter **460**. A control input of inverter **460** might be connected to a sen2b control signal node **461**. A control input of inverter **458** might be connected to a lat2b control signal node **459**.

[0078] Control logic (e.g., **116** of FIG. **1**) might be connected to the src_gate control signal node **404**, the dw_gate control signal node **402**, the blclamp control signal node **406**, the blclamp2 control signal node **408**, the en_data control signal node **410**, the tc_iso control signal node **412**, the BLC1 control signal node **420**, the sen control signal node **422**, the sab_bl_pre control signal node **454**, the en_sspc2 control signal node **434**, the dl_set control signal node **436**, the d_latch control signal node **450**, the tdcint_dis control signal node **438**, the en_sa control signal node **456**, the lat_sab control signal node **430**, the sen_sab control signal node **428**, the drst_sa control signal node **424**, the dst_sa control signal node **426**, the sen2b control signal node **461**, the lat2b control signal node **459**, the drst2 control signal node **444**, and the dst2 control signal node **446** to control

the operation of page buffer circuit **400**.

[0079] Page buffer circuit **400** might be used to sense the data state of the selected memory cell of the NAND string **206** and latch the sensed data state in sense amplifier latch **431** during a read operation or a verify phase of a programming operation. Page buffer circuit **400** might also be used to program a target data state to the selected memory cell based on a state of the sense amplifier latch **431** or a state of one or more data latches. Additional data latches (not shown in FIGS. **4**A-**4**B) might be connected in parallel with, and have a similar (e.g., same) structure as, the data latch **462**.

[0080] FIG. **5**A is a timing diagram depicting voltage levels of data lines and a selected access line for a Single SSPC programming operation. Trace **572** might represent the voltage level of a selected access line of the Single SSPC programming operation, e.g., the selected access line might be connected to control gates of a plurality of memory cells selected for programming during the programming operation. Trace **580**.sub.0 might represent the voltage level of a data line that is selectively connected to one of the selected memory cells for which programming is to be fully enabled. Trace **580**.sub.1 might represent the voltage level of a data line that is selectively connected to one of the selected memory cells for which programming is to be partially enabled. Trace **580**.sub.2 might represent the voltage level of a data line that is selectively connected to one of the selected memory cells for which programming is to be inhibited.

[0081] In FIG. **5**A, traces **572**, **580**.sub.0, **580**.sub.1, and **580**.sub.2 might have an initial voltage level **574**, e.g., a reference potential. The reference potential might be ground, 0V, or the supply voltage Vss, for example. Trace **572** might then be increased to a pass voltage **576**. Although not depicted, each unselected access line, e.g., each access line connected to a NAND string other than the selected access line, might also be increased to the pass voltage **576**. The pass voltage might be some voltage level configured to activate a memory cell of the NAND string regardless of its data state. Trace **572** might subsequently be increased to a programming voltage **578**. Although not depicted, each unselected access line might remain at the pass voltage **576**.

[0082] Prior to increasing trace **572** to the programming voltage **578**, trace **580**.sub.2 might be increased to an inhibit voltage **584** while trace **580**.sub.1 might be increased to an SSPC voltage **582**. Trace **580**.sub.0 might remain at the initial voltage level **574**, which might also represent an enable voltage **575**. Memory cells receiving the programming voltage **578** at their control gates might be expected to have a change (e.g., increase) in threshold voltage dependent upon the level of enablement for programming. For example, a memory cell whose corresponding data line is at the enable voltage **575** might be expected to have a first level of change in threshold voltage, a memory cell whose corresponding data line is at the inhibit voltage **584** might be expected to have no, or a de minimis, change in threshold voltage, and a memory cell whose corresponding data line is at the SSPC voltage **582** might be expected to have a second level of change in threshold voltage that is less than the first level of change, but greater than no change in threshold voltage.

[0083] FIG. **5**B conceptually depicts the threshold voltage changes for different groupings of memory cells of the programming operation of FIG. **5**A. Memory cells having threshold voltages in the range of threshold voltages **586**.sub.0 might have their corresponding data line configured to receive the enable voltage **575** during programming, and might be expected to experience a first level of change in threshold voltage represented by trace **588**.sub.0 in response to the programming voltage on their control gates. Memory cells having threshold voltages in the range of threshold voltages **586**.sub.1 might have their corresponding data line configured to receive the SSPC voltage **582** during programming, and might be expected to experience a second level of change in threshold voltage represented by trace **588**.sub.1 in response to the programming voltage on their control gates. Memory cells having threshold voltages in the range of threshold voltages **586**.sub.2 might have their corresponding data line configured to receive the inhibit voltage **584** during programming, and might be expected to have no, or a de minimis, change in threshold voltage.

[0084] A resulting distribution of threshold voltages **590** might be expected to be more narrow than

a programming operation not utilizing SSPC techniques. For example, if memory cells having threshold voltages in the range of threshold voltages **586**.sub.1 had their corresponding data line configured to receive the enable voltage **575** during programming, they might be expected to experience the first level of change in threshold voltage **588**.sub.0 in response to the programming voltage on their control gates, which might be expected to lead to a widening of the distribution of threshold voltages versus those memory cells experiencing the second level of change in threshold voltage **588**.sub.1.

[0085] FIG. **6**A is a timing diagram depicting voltage levels of data lines and a selected access line for a Dual SSPC programming operation. Trace **672** might represent the voltage level of a selected access line of the Dual SSPC programming operation, e.g., the selected access line might be connected to control gates of a plurality of memory cells selected for programming during the programming operation. Trace **680**.sub.0 might represent the voltage level of a data line that is selectively connected to one of the selected memory cells for which programming is to be fully enabled. Trace **680**.sub.1 might represent the voltage level of a data line that is selectively connected to one of the selected memory cells for which programming is to be partially enabled to a first level. Trace **680**.sub.2 might represent the voltage level of a data line that is selectively connected to one of the selected memory cells for which programming is to be partially enabled to a second level, lesser enabled than the first level. Trace **680**.sub.3 might represent the voltage level of a data line that is selectively connected to one of the selected memory cells for which programming is to be inhibited.

[0086] In FIG. **6**A, traces **672**, **680**.sub.0, **680**.sub.1, **680**.sub.2, and **680**.sub.3 might have an initial voltage level **674**, e.g., a reference potential. The reference potential might be ground, 0V, or the supply voltage Vss, for example. Trace **672** might then be increased to a pass voltage **676**. Although not depicted, each unselected access line, e.g., each access line connected to a NAND string other than the selected access line, might also be increased to the pass voltage **676**. The pass voltage might be some voltage level configured to activate a memory cell of the NAND string regardless of its data state. Trace **672** might subsequently be increased to a programming voltage **678**. Although not depicted, each unselected access line might remain at the pass voltage **676**.

[0087] Prior to increasing trace **672** to the programming voltage **678**, trace **680**.sub.3 might be increased to an inhibit voltage **684** while trace **680**.sub.1 might be increased to a first SSPC voltage **682**.sub.1 and trace **680**.sub.2 might be increased to a second SSPC voltage **682**.sub.2. Trace **680**.sub.0 might remain at the initial voltage level **674**, which might also represent an enable voltage **675**. Memory cells receiving the programming voltage **678** at their control gates might be expected to have a change (e.g., increase) in threshold voltage dependent upon the level of enablement for programming. For example, a memory cell whose corresponding data line is at the enable voltage **675** might be expected to have a first level of change in threshold voltage, a memory cell whose corresponding data line is at the inhibit voltage **684** might be expected to have no, or a de minimis, change in threshold voltage, a memory cell whose corresponding data line is at the first SSPC voltage **682**.sub.1 might be expected to have a second level of change in threshold voltage that is less than the first level of change, but greater than no change in threshold voltage, and a memory cell whose corresponding data line is at the second SSPC voltage **682**.sub.2 might be expected to have a third level of change in threshold voltage that is less than the second level of change, but greater than no change in threshold voltage.

[0088] FIG. **6**B conceptually depicts the threshold voltage changes for different groupings of memory cells of the programming operation of FIG. **6**A. Memory cells having threshold voltages in the range of threshold voltages **686**.sub.0 might have their corresponding data line configured to receive the enable voltage **675** during programming, and might be expected to experience a first level of change in threshold voltage represented by trace **688**.sub.0 in response to the programming voltage on their control gates. Memory cells having threshold voltages in the range of threshold voltages **686**.sub.1 might have their corresponding data line configured to receive the first SSPC

voltage **682**.sub.1 during programming, and might be expected to experience a second level of change in threshold voltage represented by trace **688**.sub.1 in response to the programming voltage on their control gates. Memory cells having threshold voltages in the range of threshold voltages **686**.sub.2 might have their corresponding data line configured to receive the second SSPC voltage **682**.sub.2 during programming, and might be expected to experience a third level of change in threshold voltage represented by trace **688**.sub.2 in response to the programming voltage on their control gates. Memory cells having threshold voltages in the range of threshold voltages **686**.sub.3 might have their corresponding data line configured to receive the inhibit voltage **684** during programming, and might be expected to have no, or a de minimis, change in threshold voltage.

[0089] A resulting distribution of threshold voltages **690** might be expected to be more narrow than the distribution of threshold voltages **590** of the Single SSPC programming operation using a same set of programming voltages. For example, as memory cells having threshold voltages closer to the range of threshold voltages **686**.sub.3 are configured to experience smaller changes in threshold voltages, narrower distributions of threshold voltages might be attained. While the Dual SSPC programming operation provides the benefit of a narrower distribution of threshold voltages over the Single SSPC programming operation, the Dual SSPC programming operation generally requires the identification of an additional range of threshold voltages over the Single SSPC programming operation and is thus generally more time consuming.

[0090] FIG. **7**A is a timing diagram depicting voltage levels of data lines and a selected access line for a programming operation in accordance with an embodiment, which might be referred to herein as Analog SSPC. For example, each memory cell not intended to be fully enabled for programming or inhibited from programming, might have a respective SSPC voltage level applied to its corresponding data line during programming that is higher than the enable voltage and lower than the inhibit voltage. Note that the use of positive voltage levels for an enable voltage are known, such that the enable voltage need not be the reference potential.

[0091] The respective SSPC voltage for a memory cell might have an inverse relationship with the I.sub.string current level of that memory cell during a verify phase of the programming operation. For example, memory cells exhibiting higher current levels during the verify phase of the programming operation might be expected to have their corresponding data line at a voltage level closer to the enable voltage for a subsequent programming pulses than memory cells exhibiting lower current levels during the verify phase of the programming operation.

[0092] Trace **772** might represent the voltage level of a selected access line of the Analog SSPC programming operation, e.g., the selected access line might be connected to control gates of a plurality of memory cells selected for programming during the programming operation. Trace **780**.sub.0 might represent the voltage level of a data line that is selectively connected to one of the selected memory cells for which programming is to be fully enabled. The shaded traces **780**.sub.1-**780**.sub.X might represent the voltage levels of data lines that are selectively connected to one of the selected memory cells for which programming is to be partially enabled to one of a plurality of levels. Trace **780**.sub.X+1 might represent the voltage level of a data line that is selectively connected to one of the selected memory cells for which programming is to be inhibited.

[0093] In FIG. **7**A, traces **772** and **780**.sub.0-**780**.sub.X+1 might have an initial voltage level **774**, e.g., a reference potential. The reference potential might be ground, 0V, or the supply voltage Vss, for example. Trace **772** might then be increased to a pass voltage **776**. Although not depicted, each unselected access line, e.g., each access line connected to a NAND string other than the selected access line, might also be increased to the pass voltage **776**. The pass voltage might be some voltage level configured to activate a memory cell of the NAND string regardless of its data state. Trace **772** might subsequently be increased to a programming voltage **778**. Although not depicted, each unselected access line might remain at the pass voltage **776**.

[0094] Prior to increasing trace **772** to the programming voltage **778**, trace **780**.sub.X+1 might be increased to an inhibit voltage **784**, while traces **780**.sub.1-**780**.sub.X might be increased to their

respective SSPC voltages **782**.sub.1-**780**.sub.X. Trace **780**.sub.0 might remain at the initial voltage level **774**, which might also represent an enable voltage **775**. Memory cells receiving the programming voltage **778** at their control gates might be expected to have a change (e.g., increase) in threshold voltage dependent upon the level of enablement for programming. For example, a memory cell whose corresponding data line is at the enable voltage **775** might be expected to have a first level of change in threshold voltage, a memory cell whose corresponding data line is at the inhibit voltage **784** might be expected to have no, or a de minimis, change in threshold voltage, and a memory cell whose corresponding data line is at one of the SSPC voltages **782**.sub.1-**782**.sub.X might be expected to have one of a number of different levels of change in threshold voltage that are each less than (e.g., less than or equal to) the first level of change, and greater than (e.g., greater than or equal to) no change in threshold voltage.

[0095] FIG. **7**B conceptually depicts the threshold voltage changes for different groupings of memory cells of the programming operation of FIG. **7**A. Memory cells having threshold voltages in the range of threshold voltages **786**.sub.0 might have their corresponding data line configured to receive the enable voltage **775** during programming, and might be expected to experience a first level of change in threshold voltage represented by trace **788**.sub.0 in response to the programming voltage on their control gates. Memory cells having threshold voltages in the range of threshold voltages **786**.sub.1-**786**.sub.X might have their corresponding data lines configured to receive one of the SSPC voltages **782**.sub.1-**782**.sub.X during programming, and might be expected to experience one of a number of different levels of change in threshold voltage represented by traces **788**.sub.1-**788**.sub.X in response to the programming voltage on their control gates. Memory cells having threshold voltages in the range of threshold voltages **786**.sub.X+1 might have their corresponding data line configured to receive the inhibit voltage **784** during programming, and might be expected to have no, or a de minimis, change in threshold voltage.

[0096] A resulting distribution of threshold voltages **790** might be expected to be more narrow than the distribution of threshold voltages **690** of the Dual SSPC programming operation using a same set of programming voltages. For example, embodiments herein can set an SSPC voltage for each memory cell that is to be partially enabled for programming in response to its own threshold voltage rather than assigning each to different ranges of threshold voltages. In addition, as will be described in more detail infra, embodiments described herein do not need to identify additional ranges of threshold voltages over a Single SSPC programming operation, thus providing certain efficiencies as well.

[0097] FIG. **8** shows a plot of an access line voltage versus time of a programming operation in accordance with embodiments. Depicted in FIG. **8** is a series of programming pulses **802** (e.g., programming pulses **802**.sub.0-**802**.sub.7), which might each be followed by a verify pulse **804** (e.g., verify pulses **804**.sub.0-**804**.sub.7). FIG. **8** might correspond to a programming operation for a TLC memory, programming memory cells to one of eight different threshold voltage distributions such as depicted in FIG. **3**A. Although seven programming pulses **802** are depicted in FIG. **8**, programming operations might utilize different numbers (e.g., greater numbers) of programming pulses **802**.

[0098] In FIG. **8**, the programming pulses **802** are depicted to have a programming start voltage, e.g., of an initial programming pulse **802**.sub.0, having a voltage level **806**. Each subsequent programming pulse might be higher than its immediately prior programming pulse **802**. During the programming pulse **802**.sub.0, each memory cell selected for programming to any data state of a plurality of data states for the programming operation other than a lowest (e.g., erased or L0) data state might be fully enabled for programming. That is, their corresponding data lines might be configured to receive an enable voltage level for the programming operation during the programming pulse **802**.sub.0. The L0 memory cells might be inhibited from programming during the programming pulse **802**.sub.0. That is, their corresponding data lines might be configured to receive an inhibit voltage level for the programming operation during the programming pulse

802.sub.0. The L0 memory cells might further be inhibited from programming for each remaining programming pulse **802**.sub.1-**802**.sub.7.

[0099] Following the programming pulse **802**.sub.0 in a programming phase of the programming operation, a verify pulse **804**.sub.1 might be applied in a verify phase of the programming operation. The verify pulse **804**.sub.1 might have a voltage level corresponding to a lowest threshold voltage for the L1 data state, e.g., the threshold voltage distribution **303**.sub.1. During this verify phase, a value of VgVt might be determined (e.g., estimated) for memory cells having the L1 data state as their intended data state. The value of VgVt represents a difference between the applied voltage level across a memory cell and its resulting threshold voltage. For example, if a voltage level of 13 volts is applied to a control gate of a memory cell whose body (e.g., channel) is at a ground potential (e.g., 0 volts), and the resulting threshold voltage is −0.5 volt, the VgVt for that memory cell is (13 volts−0 volts)−(−0.5 volts)=13.5 volts. From the value of VgVt for a group of memory cells (e.g., the memory cells selected for programming that have not yet verified), a voltage level of a subsequent programming pulse, e.g., programming pulse **802**.sub.1, might be determined that is deemed sufficient to move a fully enabled L1 memory cell to the desired threshold voltage or above, e.g., higher than or equal to the voltage level of the verify pulse **804**.sub.1. For example, a representative threshold voltage for a group of memory cells might be determined. The representative threshold voltage might represent a median of an expected normal distribution of the threshold voltages of the memory cells following the prior programming pulse, which might be determined or estimated in manners well understood in the relevant art. A value of VgVt could be determined from the voltage level of the prior programming pulse and the resulting representative threshold voltage of the group of memory cells, and a voltage level of a subsequent programming pulse could be determined in response to the value of VgVt and the desired threshold voltage (e.g., desired minimum and/or maximum threshold voltage) of the L1 memory cells.

[0100] Following the verify pulse **804**.sub.1, the programming pulse **802**.sub.1 might be applied in a programming phase of the programming operation. During the programming pulse **802**.sub.1, each memory cell selected for programming to any data state of the plurality of data states for the programming operation higher than the L1 data state might be fully enabled for programming. The L1 memory cells might be inhibited from programming, fully enabled for programming, or partially enabled for programming as determined during the verify phase of the programming operation using the verify pulse **804**.sub.1. The L1 memory cells might be subsequently inhibited from programming for each remaining programming pulse **802**.sub.2-**802**.sub.7.

[0101] Following the programming pulse **802**.sub.1, a verify pulse **804**.sub.2 might be applied in a verify phase of the programming operation. The verify pulse **804**.sub.2 might have a voltage level corresponding to a lowest threshold voltage for the L2 data state, e.g., the threshold voltage distribution **303**.sub.2. During this verify phase, a value of VgVt might be determined (e.g., estimated) for memory cells having the L2 data state as their intended data state. From this value of VgVt, a voltage level of a subsequent programming pulse, e.g., programming pulse **802**.sub.2, might be determined that is deemed sufficient to move a fully enabled L2 memory cell to the desired threshold voltage or above, e.g., higher than or equal to the voltage level of the verify pulse **804**.sub.2.

[0102] Following the verify pulse **804**.sub.2, the programming pulse **802**.sub.2 might be applied in a programming phase of the programming operation. During the programming pulse **802**.sub.2, each memory cell selected for programming to any data state of the plurality of data states for the programming operation higher than the L2 data state might be fully enabled for programming. The L2 memory cells might be inhibited from programming, fully enabled for programming, or partially enabled for programming as determined during the verify phase of the programming operation using the verify pulse **804**.sub.2. The L2 memory cells might be subsequently inhibited from programming for each remaining programming pulse **802**.sub.3-**802**.sub.7.

[0103] Following the programming pulse **802**.sub.2, a verify pulse **804**.sub.3 might be applied in a

verify phase of the programming operation. The verify pulse **804**.sub.3 might have a voltage level corresponding to a lowest threshold voltage for the L3 data state, e.g., the threshold voltage distribution **303**.sub.3. During this verify phase, a value of VgVt might be determined (e.g., estimated) for memory cells having the L3 data state as their intended data state. From this value of VgVt, a voltage level of a subsequent programming pulse, e.g., programming pulse **802**.sub.3, might be determined that is deemed sufficient to move a fully enabled L3 memory cell to the desired threshold voltage or above, e.g., higher than or equal to the voltage level of the verify pulse **804**.sub.3.

[0104] Following the verify pulse **804**.sub.3, the programming pulse **802**.sub.3 might be applied in a programming phase of the programming operation. During the programming pulse **802**.sub.3, each memory cell selected for programming to any data state of the plurality of data states for the programming operation higher than the L3 data state might be fully enabled for programming. The L3 memory cells might be inhibited from programming, fully enabled for programming, or partially enabled for programming as determined during the verify phase of the programming operation using the verify pulse **804**.sub.3. The L3 memory cells might be subsequently inhibited from programming for each remaining programming pulse **802**.sub.4-**802**.sub.7.

[0105] Following the programming pulse **802**.sub.3, a verify pulse **804**.sub.4 might be applied in a verify phase of the programming operation. The verify pulse **804**.sub.4 might have a voltage level corresponding to a lowest threshold voltage for the L4 data state, e.g., the threshold voltage distribution **303**.sub.4. During this verify phase, a value of VgVt might be determined (e.g., estimated) for memory cells having the L4 data state as their intended data state. From this value of VgVt, a voltage level of a subsequent programming pulse, e.g., programming pulse **802**.sub.4, might be determined that is deemed sufficient to move a fully enabled L4 memory cell to the desired threshold voltage or above, e.g., higher than or equal to the voltage level of the verify pulse **804**.sub.4.

[0106] Following the verify pulse **804**.sub.4, the programming pulse **802**.sub.4 might be applied in a programming phase of the programming operation. During the programming pulse **802**.sub.4, each memory cell selected for programming to any data state of the plurality of data states for the programming operation higher than the L4 data state might be fully enabled for programming. The LA memory cells might be inhibited from programming, fully enabled for programming, or partially enabled for programming as determined during the verify phase of the programming operation using the verify pulse **804**.sub.4. The LA memory cells might be subsequently inhibited from programming for each remaining programming pulse **802**.sub.5-**802**.sub.7.

[0107] Following the programming pulse **802**.sub.4, a verify pulse **804**.sub.5 might be applied in a verify phase of the programming operation. The verify pulse **804**.sub.5 might have a voltage level corresponding to a lowest threshold voltage for the L5 data state, e.g., the threshold voltage distribution **303**.sub.5. During this verify phase, a value of VgVt might be determined (e.g., estimated) for memory cells having the L5 data state as their intended data state. From this value of VgVt, a voltage level of a subsequent programming pulse, e.g., programming pulse **802**.sub.5, might be determined that is deemed sufficient to move a fully enabled L5 memory cell to the desired threshold voltage or above, e.g., higher than or equal to the voltage level of the verify pulse **804**.sub.5.

[0108] Following the verify pulse **804**.sub.5, the programming pulse **802**.sub.5 might be applied in a programming phase of the programming operation. During the programming pulse **802**.sub.5, each memory cell selected for programming to any data state of the plurality of data states for the programming operation higher than the L5 data state might be fully enabled for programming. The L5 memory cells might be inhibited from programming, fully enabled for programming, or partially enabled for programming as determined during the verify phase of the programming operation using the verify pulse **804**.sub.5. The L5 memory cells might be subsequently inhibited from programming for each remaining programming pulse **802**.sub.6-**802**.sub.7.

[0109] Following the programming pulse **802**.sub.5, a verify pulse **804**.sub.6 might be applied in a verify phase of the programming operation. The verify pulse **804**.sub.6 might have a voltage level corresponding to a lowest threshold voltage for the L6 data state, e.g., the threshold voltage distribution **303**.sub.6. During this verify phase, a value of VgVt might be determined (e.g., estimated) for memory cells having the L6 data state as their intended data state. From this value of VgVt, a voltage level of a subsequent programming pulse, e.g., programming pulse **802**.sub.6, might be determined that is deemed sufficient to move a fully enabled L6 memory cell to the desired threshold voltage or above, e.g., higher than or equal to the voltage level of the verify pulse **804**.sub.6.

[0110] Following the verify pulse **804**.sub.6, the programming pulse **802**.sub.6 might be applied in a programming phase of the programming operation. During the programming pulse **802**.sub.6, each memory cell selected for programming to any data state of the plurality of data states for the programming operation higher than the L6 data state might be fully enabled for programming. The L6 memory cells might be inhibited from programming, fully enabled for programming, or partially enabled for programming as determined during the verify phase of the programming operation using the verify pulse **804**.sub.6. The L6 memory cells might be subsequently inhibited from programming for the remaining programming pulse **802**.sub.7.

[0111] Following the programming pulse **802**.sub.6, a verify pulse **804**.sub.7 might be applied in a verify phase of the programming operation. The verify pulse **804**.sub.7 might have a voltage level corresponding to a lowest threshold voltage for the L7 data state, e.g., the threshold voltage distribution **303**.sub.7. During this verify phase, a value of VgVt might be determined (e.g., estimated) for memory cells having the L7 data state as their intended data state. From this value of VgVt, a voltage level of a subsequent programming pulse, e.g., programming pulse **802**.sub.7, might be determined that is deemed sufficient to move a fully enabled L7 memory cell to the desired threshold voltage or above, e.g., higher than or equal to the voltage level of the verify pulse **804**.sub.7.

[0112] Following the verify pulse **804**.sub.7, the programming pulse **802**.sub.7 might be applied in a programming phase of the programming operation. During the programming pulse **802**.sub.7, the L7 memory cells might be inhibited from programming, fully enabled for programming, or partially enabled for programming as determined during the verify phase of the programming operation using the verify pulse **804**.sub.7.

[0113] It is recognized that presuming memory cells to have reached their desired threshold voltages without further verification might result in memory cells having threshold voltages below their desired threshold voltages. However, the number of such memory cells might be expected to be small given the relatively small change in threshold voltage necessary for each data state, and error correction schemes are generally capable of correcting such erroneous data.

[0114] FIG. **9** is a conceptual depiction of the programming operation of FIG. **8**. Following application of the programming pulse **802**.sub.0, a threshold voltage distribution **910**.sub.0 might result containing memory cells having the intended data states L1-L7. An upper voltage level of the threshold voltage distribution **910**.sub.0 might be lower than or equal to an upper voltage level of the L1 data state, or L1_max. This might be accomplished by selecting a voltage level of the programming pulse **802**.sub.0, Vpgm_init, satisfying the following equation:

[00001] $Vpgm_init - VgVt + 3PVS < L1_max \quad Eq.1$

[0115] In Equation 1, the value of VgVt might correspond to a representative value of VgVt for the memory cells selected for programming, which might, for example, be predetermined experimentally, empirically or through simulation based on known characteristics (e.g., intrinsic properties) of the memory cells. The value of PVS might correspond to a value (in volt unit per sigma) of one standard deviation (e.g., one sigma of a normal distribution of threshold voltages of the memory cells) responsive to a programming pulse. The value of PVS might, for example, be predetermined experimentally, empirically or through simulation based on known characteristics

(e.g., intrinsic properties) of the memory cells. The value of L1_max might be predetermined, and might be equal to a voltage level of the verify pulse **804**.sub.1 plus a desired state width for the L1 data state, e.g., the width of the threshold voltage distribution **330**.sub.1 of FIG. **3**A. Note that the desired state width for each data state other than L0 might have a same value. Alternatively, desired state widths could be independently defined.

[0116] The voltage level of the programming pulse **802**.sub.1 might be determined as a sum of the voltage level of the prior programming pulse, e.g., Vpgm_init, plus a step voltage level, e.g., Vpgm_step, satisfying the following equation:

[00002] $Vpgm_step > 7PVS - SW \quad Eq.2$

[0117] In Equation 2, the value of SW might correspond to the desired state width for the L1 data state. Alternatively, the voltage level of the programming pulse **802**.sub.1 might be determined in a similar manner as used for the programming pulse **802**.sub.0, modifying Equation 1 to use a value of VgVt determined in response to applying the verify pulse **804**.sub.1, and replacing L1_max with an upper voltage level of the L2 data state, or L2_max. The value of L2_max might be predetermined, and might be equal to a voltage level of the verify pulse **804**.sub.2 plus a desired state width for the L2 data state, e.g., the width of the threshold voltage distribution **330**.sub.2 of FIG. **3**A. Memory cells having a desired data state of L1 might be enabled (e.g., fully enabled or partially enabled) for programming, or inhibited from programming, for the programming pulse **802**.sub.1 depending upon their level of activation in response to applying the verify pulse **804**.sub.1. Memory cells having a desired data state of L2 or higher might be enabled (e.g., fully enabled) for programming for the programming pulse **802**.sub.1.

[0118] Following application of the programming pulse **802**.sub.1, a threshold voltage distribution **910**.sub.1 might result containing memory cells having the intended data states L2-L7, and a threshold voltage distribution **912**.sub.1 might result containing memory cells having the intended data state L1. The programming pulse **802**.sub.1 thus might be considered a fine programming pulse for the L1 memory cells, and a sampling pulse for the L2 memory cells. The threshold voltage distribution **912**.sub.1 might have a lower voltage level **914**.sub.1 and an upper voltage level **916**.sub.1, and might correspond to the threshold voltage distribution **330**.sub.1. The lower voltage level **914**.sub.1 might correspond to the voltage level of the verify pulse **804**.sub.1.

[0119] The voltage level of the programming pulse **802**.sub.2 might be determined as a sum of the voltage level of the prior programming pulse plus a step voltage level, using the voltage level of the programming pulse **802**.sub.1 as the prior programming pulse, and using the state width of the L3 data state. Alternatively, the voltage level of the programming pulse **802**.sub.2 might be determined in response to a value of VgVt determined in response to applying the verify pulse **804**.sub.2, and using an upper voltage level of the L3 data state as the limit. Memory cells having a desired data state of L2 might be enabled (e.g., fully enabled or partially enabled) for programming, or inhibited from programming, for the programming pulse **802**.sub.2 depending upon their level of activation in response to applying the verify pulse **804**.sub.2. Memory cells having a desired data state of L3 or higher might be enabled (e.g., fully enabled) for programming for the programming pulse **802**.sub.2.

[0120] Following application of the programming pulse **802**.sub.2, a threshold voltage distribution **910**.sub.2 might result containing memory cells having the intended data states L3-L7, and a threshold voltage distribution **912**.sub.2 might result containing memory cells having the intended data state L2. The programming pulse **802**.sub.2 thus might be considered a fine programming pulse for the L2 memory cells, and a sampling pulse for the L3 memory cells. The threshold voltage distribution **912**.sub.2 might have a lower voltage level **914**.sub.2 and an upper voltage level **916**.sub.2, and might correspond to the threshold voltage distribution **330**.sub.2. The lower voltage level **914**.sub.2 might correspond to the voltage level of the verify pulse **804**.sub.2.

[0121] The voltage level of the programming pulse **802**.sub.3 might be determined as a sum of the voltage level of the prior programming pulse plus a step voltage level, using the voltage level of the

programming pulse **802**.sub.2 as the prior programming pulse, and using the state width of the L4 data state. Alternatively, the voltage level of the programming pulse **802**.sub.3 might be determined in response to a value of VgVt determined in response to applying the verify pulse **804**.sub.3, and using an upper voltage level of the L4 data state as the limit. Memory cells having a desired data state of L3 might be enabled (e.g., fully enabled or partially enabled) for programming, or inhibited from programming, for the programming pulse **802**.sub.3 depending upon their level of activation in response to applying the verify pulse **804**.sub.3. Memory cells having a desired data state of L4 or higher might be enabled (e.g., fully enabled) for programming for the programming pulse **802**.sub.3.

[0122] Following application of the programming pulse **802**.sub.3, a threshold voltage distribution **910**.sub.3 might result containing memory cells having the intended data states L4-L7, and a threshold voltage distribution **912**.sub.3 might result containing memory cells having the intended data state L3. The programming pulse **802**.sub.3 thus might be considered a fine programming pulse for the L3 memory cells, and a sampling pulse for the L4 memory cells. The threshold voltage distribution **912**.sub.3 might have a lower voltage level **914**.sub.3 and an upper voltage level **916**.sub.3, and might correspond to the threshold voltage distribution **330**.sub.3. The lower voltage level **914**.sub.3 might correspond to the voltage level of the verify pulse **804**.sub.3. This process might be continued in a like manner for each remaining programming pulse **802**.

[0123] FIG. **10** is a timing diagram generally depicting voltage levels of various nodes of a page buffer circuit such as the page buffer circuit **400** depicted in FIGS. **4**A-**4**B at various stages of a verify phase of a programming operation in accordance with an embodiment. FIG. **10** provides detail of a portion of a verify phase that might be used with embodiments. Traces **1020**.sub.0, **1020**.sub.1, and **1020**.sub.2 might each represent a respective voltage level of a data line **204** corresponding to a memory cell having a first I.sub.string value, a second I.sub.string value higher than the first I.sub.string value, and a third I.sub.string value higher than the second I.sub.string value, respectively, during the verify phase of the programming operation. Traces **1022**.sub.0, **1022**.sub.1, and **1022**.sub.2 might each represent a respective voltage level of a tc signal node **432** corresponding to the data line **204** of traces **1020**.sub.0, **1020**.sub.1, and **1020**.sub.2, respectively. Trace **1024** might represent the voltage level of the boost node **418**. Trace **1026** might represent the voltage level of the sen control signal node **422**.

[0124] With regard to FIG. **10**, a precharge portion of the verify phase of the programming operation might begin at time t**0** by precharging the tc signal node **432** and the data line **204** from an initial voltage level **1028** to a voltage level **1030**. For example, the tc signal node **432** and data line **204** might be connected to the vreg2 voltage node **414**, the sense amplifier latch **431**, or the vprech voltage node **457**. The voltage level **1030** might be higher than the inhibit voltage Vinh for the programming operation. The voltage level **1028** might be a reference potential. At time t**1**, the tc signal node **432** and the data line **204** might optionally be discharged to a voltage level **1032**. The voltage level **1032** is some voltage level lower than the voltage level **1030**, and might correspond to the inhibit voltage Vinh plus a threshold voltage of a transistor to be used as a source follower for a subsequent programming phase of the programming operation, e.g., the threshold voltage of the transistor **447**. For some embodiments, the threshold voltage of the source-follower transistor might be lower than or equal to 0V. To obtain voltage level **1031**, for example, where the inhibit voltage Vinh is equal to the supply voltage Vcc, the tc signal node **432** and the data line **204** might be connected to the voltage node **448** through the transistor **447** while the control gate of the transistor **447** is also connected to the tc signal node **432** and data line **204**, and the voltage node **448** receives the supply voltage Vcc. Doing this for each memory cell selected for programming might serve to mitigate any threshold voltage variation among the transistors **447**, or other transistors to be used as source followers, for each page buffer circuit **400** during the subsequent programming phase of the programming operation. The tc signal node **432** might then be isolated from the data line **204**.

[0125] At time t**2**, the tc signal node **432** might be boosted by applying a boost voltage level **1034** to the boost node **418**. While the boost node **418** is depicted to initially be at the same voltage level as the tc signal node **432** at time t**2**, e.g., voltage level **1028**, it could start at some other initial voltage level. After isolation of the tc signal node **432** from the data line **204**, e.g., at time t**2**, a selected memory cell for the programming operation that is connected to the data line **204** might be selectively activated in response to a voltage level of a verify pulse **804** applied to its control gate while each remaining memory cell of its string of series-connected memory cells is activated, e.g., receiving a pass voltage. As a result, the data line **204** might be selectively discharged, e.g., to the common source **216**.

[0126] For example, if the selected memory cell corresponding to the data line **204** remains deactivated in response to the verify pulse **804**, the voltage level of the data line **204** might remain unchanged from its precharge voltage level, e.g., as depicted in trace **1020**.sub.0. If the selected memory cell corresponding to the data line **204** is partially activated in response to the verify pulse **804**, the voltage level of the data line **204** might decrease at a first rate, e.g., as depicted in trace **1020**.sub.1. And if the selected memory cell corresponding to the data line **204** is fully activated in response to the verify pulse **804**, the voltage level of the data line **204** might decrease at a second rate greater than the first rate, e.g., as depicted in trace **1020**.sub.2. In general, the higher the I.sub.string current level for the string of series-connected memory cells containing the selected memory cell during the verify phase of the programming operation, the lower the resulting voltage level of its corresponding data line **204**. At time t**4**, the data line **204** might be isolated from the common source **216**. Note that the resulting voltage level of the data line **204** at time t**3** might depend on the level of activation of its corresponding selected memory cell **208** as well as the length of time that the data line **204** is permitted to selectively discharge to the common source **216**.

[0127] At time t**4**, the tc signal node **432** might be connected to its corresponding data line **204**. If the corresponding data line **204** is represented by trace **1020**.sub.0, the tc signal node **432** might decrease by a first amount, e.g., as depicted in trace **1022**.sub.0, as the data line **204** might be at the voltage level **1032** that is lower than the boosted voltage level **1036** of the tc signal node **432** despite not being discharged. If the selected memory cell corresponding to the data line **204** is partially activated in response to the verify pulse **804**, the voltage level of the tc signal node **432** might decrease by a second amount greater than the first amount, e.g., as depicted in trace **1022**.sub.1. And if the selected memory cell corresponding to the data line **204** is fully activated in response to the verify pulse **804**, the voltage level of the tc signal node **432** might decrease by a third amount greater than the second amount, e.g., as depicted in trace **1022**.sub.2. In general, the higher the I.sub.string current level for the string of series-connected memory cells containing the selected memory cell during the verify phase of the programming operation, the lower the resulting voltage level of its corresponding tc signal node **432**. At time t**4**, the tc signal node **432** might be isolated from the data line **204**. Note that the resulting voltage level of the tc signal node **432** at time t**4** might depend on the voltage level of the data line **204** and the length of time, e.g., a develop time, that the tc signal node **432** is connected to the data line **204** for discharge.

[0128] At time t**5**, the voltage level applied to the boost node **418** might be decreased to a first deboost voltage level **1042**, lower than the boost voltage level **1034**. As a result, the voltage level of the tc signal node **432** might be correspondingly decreased. At time t**6**, the page buffer circuit **400** might be strobed by transitioning the sen control signal node **422** to a logic high to activate the transistor **421** to selectively connect the sense amplifier latch **431** to the voltage node **452** through the transistor **451**. Memory cells corresponding to tc signal nodes **432** that have a voltage level lower than the threshold voltage of the transistor **451** while the first deboost voltage level **1042** is applied to the boost node **418** (e.g., as evidenced by a value latched by the SA latch **431** during the first strobe) might be flagged to receive the enable voltage, e.g., to be fully enabled for programming, during the subsequent programming phase of the programming operation.

[0129] The first deboost voltage level **1042** might be selected to identify memory cells that are deemed to have a particular threshold voltage level below the target threshold voltage level of their intended data state, e.g., the data state to be verified during the verify phase of the programming operation. These memory cells might correspond to the range of threshold voltages **786**.sub.0 in FIG. **7**B. Lower voltage levels of the first deboost voltage level **1042** might be used to shift the range of threshold voltages **786**.sub.0 in FIG. **7**B to the right, e.g., to a higher range of threshold voltages, thus fully enabling greater numbers of memory cells. Higher voltage levels of the first deboost voltage level **1042** might be used to shift the range of threshold voltages **786**.sub.0 in FIG. **7**B to the left, e.g., to a lower range of threshold voltages, thus fully enabling lesser numbers of memory cells.

[0130] At time t**7**, the voltage level applied to the boost node **418** might be decreased to a second deboost voltage level **1044**, lower than the first deboost voltage level **1042**. As a result, the voltage level of the tc signal node **432** might be correspondingly decreased. At time t**8**, the page buffer circuit **400** might be strobed by transitioning the sen control signal node **422** to a logic high to activate the transistor **421** to selectively connect the sense amplifier latch **431** to the voltage node **452** through the transistor **451**. Memory cells corresponding to tc signal nodes **432** that have voltage levels higher than (e.g., higher than or equal to) the threshold voltage of the transistor **451** while the second deboost voltage level **1044** is applied to the boost node **418** (e.g., as evidenced by a value latched by the SA latch **431** during the second strobe) might be flagged to receive the inhibit voltage, e.g., to be inhibited from programming, during the subsequent programming phase of the programming operation.

[0131] The second deboost voltage level **1044** might be selected to identify memory cells that are deemed to have a threshold voltage level higher than (e.g., higher than or equal to) the target threshold voltage level of their intended data state, e.g., the data state to be verified during the verify phase of the programming operation. These memory cells might correspond to the range of threshold voltages **786**.sub.X+1 in FIG. **7**B. Higher voltage levels of the second deboost voltage level **1044** might be used to shift the range of threshold voltages **786**.sub.X+1 in FIG. **7**B to the right, e.g., to a higher range of threshold voltages, thus inhibiting greater numbers of memory cells. Lower voltage levels of the second deboost voltage level **1044** might be used to shift the range of threshold voltages **786**.sub.X+1 in FIG. **7**B to the left, e.g., to a lower range of threshold voltages, thus inhibiting lesser numbers of memory cells.

[0132] It is noted that the number of memory cells selected for programming that indicate deactivation of the transistor **451** for each deboost voltage level might provide information for determining a VgVt value for the memory cells selected for programming. In particular, the number of memory cells that indicate deactivation at the first deboost voltage level **1042** would indicate a number of memory cells having a threshold voltage level lower than or equal to a first threshold voltage level, and the number of memory cells that indicate deactivation at the second deboost voltage level **1044** would indicate a number of memory cells having a threshold voltage level lower than or equal to a second threshold voltage level that is higher than the first threshold voltage level. Where a normal distribution of threshold voltages is presumed, these two data points could define characteristics of the normal distribution, e.g., the median of the normal distribution.

[0133] Identifying memory cells to be fully enabled for programming, or to be inhibited from programming, during a subsequent programming phase might further identify memory cells to be partially enabled for programming for the subsequent programming phase. For example, memory cells selected for programming to the data state to be verified by the verify phase of the programming operation that are not identified to be fully enabled for programming for the subsequent programming phase, and are not identified to be inhibited from programming for the subsequent programming phase, might represent those memory cells to be partially enabled for programming for the subsequent programming phase. The data lines corresponding to these memory cells might then be configured to receive a voltage level for the subsequent programming

phase from a source-follower transistor in accordance with embodiments.

[0134] At time t**9**, the voltage level applied to the boost node **418** might be returned to its initial voltage level, e.g., the voltage level **1028**. As a result, the voltage level of the tc signal node **432** might be correspondingly decreased. At time t**10**, the remaining voltage level of the tc signal node **432** might be indicative of the threshold voltage of its corresponding memory cell. For example, tc signal nodes **432** having voltage levels closer to the precharge voltage level, e.g., the voltage level **1032** (or **1030**), might be expected to have threshold voltage levels closer to their respective target data states, while tc signal nodes **432** having voltage levels closer to the initial voltage level, e.g., the voltage level **1028**, might be expected to have threshold voltage levels farther from their respective target data states. For those tc signal nodes **432** whose corresponding memory cells were not flagged to either receive the enable voltage or the inhibit voltage for a subsequent programming pulse might be flagged to receive a data line voltage level representative of, which might include equal to, the remaining voltage level of that tc signal node **432**. These memory cells might correspond to the range of threshold voltages **786**.sub.1-**786**.sub.X in FIG. **7**B.

[0135] At time t**10**, the control gate of the transistor to be used as a source follower might be connected to the tc signal node **432**, thus applying a voltage level at the control gate representative of the remaining voltage level of the tc signal node **432**. Using the transistor **447** as an example, the transistors **449**, **435**, and **419** might be activated. While transistors **449**, **435**, and **419** are activated, the transistor **433** might be deactivated in response to the en_sspc2 control signal node **434**. In this manner, the tc signal node **432** might be isolated from the voltage node **448**. This might connect the voltage level of the tc signal node **432**, or a voltage level representative of the voltage level of the tc signal node **432**, to the control gate of the transistor **447**. The transistor **449** and/or the transistor **435** might subsequently be deactivated, leaving the control gate of the transistor **447** electrically floating with a voltage level representative to the voltage level of the tc signal node **432**.

[0136] For a subsequent programming pulse, a voltage level higher than the enable voltage level might be applied to the voltage node **448** while the transistor **447** is connected to the data line **204** and its control gate remains electrically floating at a voltage level representative of the remaining voltage level of the tc signal node **432** following the verify phase of the programming operation. For example, the transistor **449** and/or the transistor **435** might remain deactivated, and the transistors **433**, **419**, **411**, **405**, and **401** might be activated to connect the transistor **447** to the data line **204**. In this manner, the data line **204** might receive a voltage level that is lower than or equal to the voltage level applied to the voltage node **448**, which might further be higher than (e.g., higher than or equal to) the enable voltage. For some embodiments, the voltage level applied to the voltage node **448** might be equal to the inhibit voltage Vinh. For further embodiments, the voltage level applied to the voltage node **448** might be higher than the inhibit voltage Vinh.

[0137] It is recognized that the length of time the data line **204** is permitted to selectively discharge through the memory cell from time t**2**-t**3** of FIG. **10**, and the length of time the tc signal node **432** is permitted to discharge to the data line **204** from time t**3**-t**4** of FIG. **10**, will each affect the extent of discharge of the tc signal node **432** at time t**4** of FIG. **10**. Determining suitable lengths of time, as well as suitable boost and deboost voltage levels, to identify groups of memory cells that should be fully enabled for programming and groups of memory cells that should be inhibited from programming, might, for example, be determined experimentally, empirically or through simulation based on known characteristics (e.g., intrinsic properties) of the participating circuit elements.

[0138] Although the transistor **447** of the page buffer circuit **400** was utilized as the source-follower transistor in the foregoing example, a source-follower transistor to be used for various embodiments could be another transistor that has a control gate connected or selectively connected to a node of a page buffer circuit whose voltage level is indicative of a data state of a memory cell following a verify phase of a programming operation, a source/drain selectively connected to a corresponding data line of the memory cell, and another source/drain configured to receive a voltage level for driving the corresponding data line during a subsequent programming phase of the

programming operation. Note that such guidance can be applied to page buffer circuits of designs other than that depicted in FIGS. **4**A-**4**B. FIGS. **11**A and **11**B depict alternate examples of suitable source-follower transistors for use with embodiments.

[0139] Semiconductor capacitors might be formed as a transistor that is not configured for current flow, such as by deadheading one or both source/drain regions of the transistor. FIG. **11**A depicts how the sense capacitor **417** might be formed as a transistor that could be further utilized as a source-follower transistor. In FIG. **11**A, the sense capacitor **417** might be a transistor **1150** having its control gate connected to the tc signal node **432**, having a first source/drain connected to the voltage node **418**, and having a second source/drain connected to a first source/drain of transistor **1152**. The control gate of the transistor **1152** might be connected to a control signal node **1154**, which might be in communication with the control logic **116**. Although the second source/drain of transistor **1152** is depicted to be connected to the first source/drain of the transistor **411**, it could be connected anywhere between a transistor isolating the tc signal node **432** from the data line **204** and the data line **204** itself. In the example of FIG. **11**A, the second source/drain of transistor **1152** might thus alternatively be connected between the transistor **405** and the transistor **401**, or connected directly to the data line **204**.

[0140] When utilizing the transistor **1150** (e.g., sense capacitor **417**) for boosting and deboosting the tc signal node **432** during the verify phase, the control signal node **1154** might receive a control signal configured to deactivate the transistor **1152**. The boost-deboost voltage levels applied to the voltage node **418** might be as described with reference to FIGS. **4**A and **10**. In preparing the transistor **1150** for driving the data line **204** during a programming phase, the voltage level of the tc signal node **432** remaining after the verify phase might be retained on the control gate of the transistor **1150** by deactivating the transistors **411** and **419** in the example of FIG. **11**A. The control signal node **1154** might then receive a control signal configured to activate the transistor **1152**. A voltage level to be applied to the voltage node **418** might then be as described with reference to the voltage level applied to voltage node **448** for use of the transistor **447** as a source-follower.

[0141] While previous examples of a source-follower transistor repurposed existing transistors of a page buffer circuit, embodiments could alternatively add a transistor to any page buffer circuit. For example, in FIG. **11**B, a transistor **1160** might be added to an existing page buffer circuit, e.g., the page buffer circuit **400**. The control gate of transistor **1160** might be connected to the tc signal node **432** or other node of a page buffer circuit that is indicative of a data state of a memory cell following a verify phase of a programming operation. A first source/drain of the transistor **1160** might be connected to a voltage node **1162**. A second source/drain of the transistor **1160** might be connected to a first source/drain of the transistor **1164**. Although the control gate of the transistor **1160** is depicted to be connected directly to the tc signal node **432**, it alternatively could be selectively connected to the tc signal node **432** anywhere in the page buffer circuit, provided that the control gate of the transistor **1160** can receive a voltage level representative of the voltage level of a node of the page buffer circuit that is indicative of a data state of a memory cell following a verify phase of a programming operation, e.g., the tc signal node **432**, and the can be made to retain that voltage level, e.g., by subsequently electrically floating the control gate.

[0142] The control gate of the transistor **1164** might be connected to a control signal node **1166**, which might be in communication with the control logic **116**. Although the second source/drain of transistor **1164** is depicted to be connected to the first source/drain of the transistor **411**, it could be connected anywhere between a transistor isolating the tc signal node **432** from the data line **204** and the data line **204** itself. In the example of FIG. **11**B, the second source/drain of transistor **1164** might thus alternatively be connected between the transistor **405** and the transistor **401**, or connected directly to the data line **204**.

[0143] In preparing the transistor **1160** for driving the data line **204** during a programming phase, the voltage level of the tc signal node **432** remaining after the verify phase might be retained on the control gate of the transistor **1160** by deactivating the transistors **411** and **419** in the example of

FIG. **11**B. The control signal node **1166** might then receive a control signal configured to activate the transistor **1164**. A voltage level to be applied to the voltage node **1162** might then be as described with reference to the voltage level applied to voltage node **448** for use of the transistor **447** as a source-follower. When not using the transistor **1160** as a source-follower for various embodiments, the control signal node **1166** might receive a control signal configured to deactivate the transistor **1164**, and the voltage node **1162** might receive a reference potential, for example.

[0144] FIGS. **12**A-**12**B depict conceptual relationships between control gate voltages of a source-follower transistor, and a voltage level (e.g., output voltage level) of a source of the transistor for a particular voltage level applied to its drain. FIG. **12**A contemplates a transistor having a positive threshold voltage, while FIG. **12**B contemplates a transistor having a threshold voltage of 0V or lower. Traces **1270** might represent the source voltage level of a transistor, while traces **1272** might represent the drain voltage level of that transistor.

[0145] In FIG. **12**A, the voltage level of the drain of the transistor, e.g., trace **1272**, might be equal to the inhibit voltage Vinh, although higher or lower voltage levels could be used. In this manner, the voltage level of the source of the transistor, e.g., trace **1270**, might be equal to the voltage level of the control gate of the transistor, minus the threshold voltage of the transistor, for voltage levels of the control gate equal to or higher than the threshold voltage **1274** of the transistor and equal to or lower than the voltage level of the drain. As such, the voltage level of the source might remain at 0V until the voltage level of the control gate is equal to the threshold voltage, and might generally increase at a slope of 1, e.g., the voltage level of the source might be expected to increase by X volts for every X-volt increase in the voltage level of the control gate. If the voltage level of the drain of the transistor is equal to the inhibit voltage Vinh plus the threshold voltage **1274** of the transistor, the voltage level of the source might be expected to have a value between 0V and the inhibit voltage Vinh, depending upon a voltage level of the control gate of the transistor.

[0146] It is known that the threshold voltage of a transistor can be modified through appropriate channel doping. As such, a transistor to be used as a source-follower could be made to have a threshold voltage at or near 0V. For embodiments using a source-follower transistor having a threshold voltage of 0V, as depicted in FIG. **12**B, the voltage level of the source, e.g., trace **1270**, might be expected to generally be equal to the voltage level of the control gate for voltage levels between 0V and the voltage level of the drain, e.g., trace **1272**. If the voltage level of the drain of the transistor is equal to the inhibit voltage Vinh, the voltage level of the source might be expected to have a value between 0V and the inhibit voltage Vinh, depending upon a voltage level of the control gate of the transistor.

[0147] FIG. **13** is a flowchart of a method of operating a memory in accordance with an embodiment. The method might represent actions associated with a programming operation, e.g., portions of a verify phase and programming phase of the programming operation, performed by the memory. The method might be in the form of computer-readable instructions, e.g., stored to the instruction registers **128**. Such computer-readable instructions might be executed by a controller, e.g., the control logic **116**, to cause the relevant components of the memory to perform the method.

[0148] At **1301**, a first voltage level indicative of a data state of a memory cell might be applied to a control gate of a transistor. The transistor might represent the transistor **447** of FIG. **4**A, the transistor **1150** of FIG. **11**A, or the transistor **1160** of FIG. **11**B, for example. The memory cell might represent a memory cell **208** selectively connected to a page buffer circuit. The first voltage level indicative of the data state of the memory cell might represent the voltage level of a node of the page buffer circuit. For example, the node of the page buffer circuit might be the tc signal node **432** of the page buffer circuit **400**, or the voltage level of a different node of the page buffer circuit **400** while connected to the tc signal node **432**, such as the control gate of the transistor **447**. The voltage level of the node of the page buffer circuit might indicate how near the memory cell is to a desired data state. Higher voltage levels might indicate that the memory cell is closer to its desired data state, while lower voltage levels might indicate that the memory cell is farther from its desired

data state. At **1303**, the first voltage level might be retained on the control gate of the transistor. For example, the control gate of the transistor might be electrically floated, e.g., isolating it from any current sink or current source. For the transistor **447** of FIG. **4**A, the transistor **449** might be deactivated to electrically float the control gate of the transistor **447**. For the transistor **1150** of FIG. **11**A, the transistors **411** and **419** might be deactivated to electrically float the control gate of the transistor **1150**. For the transistor **1160** of FIG. **11**B, the transistors **411** and **419** might be deactivated to electrically float the control gate of the transistor **1160**.

[0149] At **1305**, a first source/drain of the transistor might be connected to a data line corresponding to the memory cell while applying a second voltage level to a second source/drain of the transistor and while retaining the first voltage level on the control gate of the transistor. Using the example of the transistor **447** corresponding to the transistor in the method, the transistors **433**, **419**, **411**, **405**, and **401** might be activated to connect a source/drain of the transistor **447** to the data line **204**. The second voltage level might correspond to (e.g., be equal to) an inhibit voltage level of the programming operation, e.g., a voltage level configured to inhibit an increase in threshold voltage level of a memory cell receiving a programming voltage level on its control gate while its corresponding data line receives the inhibit voltage level. For other embodiments, the second voltage level might be higher than the inhibit voltage level.

[0150] In response to connecting the data line to the first source/drain of the transistor while applying the second voltage level to the second source/drain of the transistor and while retaining the first voltage level on the control gate of the transistor, a voltage level applied to the data line might be expected to be between the inhibit voltage level of the programming operation and an enable voltage level of the programming operation, e.g., a voltage level configured to cause an increase in threshold voltage level of a memory cell receiving the programming voltage level on its control gate while its corresponding data line receives the enable voltage level.

[0151] At **1307**, a programming pulse might be applied to a control gate of the memory cell while the data line is connected to the first source/drain of the transistor. The programming pulse might have the programming voltage level for a programming phase of the programming operation, subsequent to (e.g., immediately subsequent to) the verify phase of the programming operation producing the first voltage level at **1301**.

[0152] FIG. **14** is a flowchart of a method of operating a memory in accordance with an embodiment. The method might represent actions associated with a programming operation, e.g., portions of a verify phase and programming phase of the programming operation, performed by the memory. The method might be in the form of computer-readable instructions, e.g., stored to the instruction registers **128**. Such computer-readable instructions might be executed by a controller, e.g., the control logic **116**, to cause the relevant components of the memory to perform the method.

[0153] At **1411**, a node of a page buffer circuit might be discharged to a voltage level that is indicative of a level of current flow through a memory cell during a verify phase of a programming operation. For example, a tc signal node **432** might be discharged as described with reference to times t**3**-t**4** in FIG. **10**.

[0154] At **1413**, a voltage level might be retained on a control gate of a transistor that is representative of the voltage level of the node. For example, the control gate of the transistor might be connected to the node, then the control gate of the transistor might be electrically floated. Alternatively, for a transistor having its control gate directly connected to the node, the control gate of the transistor might be electrically floated without having to actively connect the control gate to the node. The transistor might correspond to the transistor **447** of FIG. **4**A, the transistor **1150** of FIG. **11**A, or the transistor **1160** of FIG. **11**B, for example.

[0155] The control gate of the transistor **447** might be connected to the tc signal node **432** by activating the transistors **439**, **435**, and **419**, thus receiving its voltage level representative of the voltage level of the node. That voltage level might then be retained by deactivating the transistor **449**. The control gates of the transistors **1150** and **1160** might be directly connected to the tc signal

node **432**, such that their voltage level representative of the voltage level of the node might be the voltage level of the tc signal node **432**. Their voltage levels might each be retained by deactivating the transistors **411** and **419**.

[0156] At **1415**, a first source/drain of the transistor might be connected to a data line corresponding to the memory cell while applying a particular voltage level to a second source/drain of the transistor and while continuing to electrically float the control gate of the transistor. The particular voltage level might correspond to (e.g., be equal to) an inhibit voltage level of the programming operation. For other embodiments, the particular voltage level might be higher than the inhibit voltage level. At **1417**, a programming pulse might be applied to a control gate of the memory cell while the data line is connected to the first source/drain of the transistor.

[0157] FIG. **15** is a flowchart of a method of operating a memory in accordance with an embodiment. The method might represent actions associated with a programming operation, e.g., portions of a verify phase and programming phase of the programming operation, performed by the memory. The method might be in the form of computer-readable instructions, e.g., stored to the instruction registers **128**. Such computer-readable instructions might be executed by a controller, e.g., the control logic **116**, to cause the relevant components of the memory to perform the method.

[0158] At **1521**, a data line and a node might be precharged to a first voltage level. This might correspond to times t**0**-t**2** of FIG. **10**. The first voltage level might correspond to the voltage level **1032** of FIG. **10** where the optional discharge of the data line and node is utilized, or the voltage level **1030** where it is not.

[0159] At **1523**, the node might be isolated from the data line, then a boost voltage level might be capacitively coupled to the node. This might correspond to times t**2**-t**3** of FIG. **10**. At **1525**, the data line might be selectively discharged through a memory cell in response to applying a second voltage level to a control gate of the memory cell. This might further correspond to times t**2**-t**3** of FIG. **10**. The second voltage level might correspond to a voltage level of one of the verify pulses **804** of FIG. **8**.

[0160] At **1527**, the node might be connected to the data line, then the node might be isolated from the data line. This might correspond to times t**3**-t**4** of FIG. **10**. At **1529**, a deboost voltage level, lower than the boost voltage level, might be capacitively coupled to the node. This might correspond to times t**9**-t**10** of FIG. **10**. Note that additional deboost voltage levels might be previously capacitively coupled to the node, e.g., to identify memory cells to be either fully enabled for programming, or inhibited from programming, during a subsequent programming phase of the programming operation.

[0161] At **1531**, a control gate of a transistor that is connected to the node might be electrically floated. The transistor might correspond to the transistor **447** of FIG. **4**A, the transistor **1150** of FIG. **11**A, or the transistor **1160** of FIG. **11**B, for example. The control gate of the transistor **447** might be connected to the tc signal node **432** by activating the transistors **439**, **435**, and **419**, and might then be electrically floated by deactivating the transistor **449**. The control gates of the transistors **1150** and **1160** might be directly connected to the tc signal node **432**, and might be electrically floated by deactivating the transistors **411** and **419**.

[0162] At **1533**, a first source/drain of the transistor might be connected to a data line corresponding to the memory cell while applying a third voltage level to a second source/drain of the transistor and while continuing to electrically float the control gate of the transistor. The third voltage level might correspond to (e.g., be equal to) an inhibit voltage level of the programming operation. For other embodiments, the third voltage level might be higher than the inhibit voltage level.

[0163] At **1535**, a fourth voltage level might be applied to the control gate of the memory cell while the data line is connected to the first source/drain of the transistor, wherein the fourth voltage level is configured to increase a threshold voltage of the memory cell, e.g., while the data line is receiving a voltage level from the first source/drain of the transistor. The fourth voltage level might

be a voltage level of a programming pulse determined in response to a value of VgVt for a group of memory cells, e.g., a group of memory cells having a same desired data state for the programming operation, resulting from a prior (e.g., immediately prior) programming pulse, and a desired threshold voltage for that desired data state, e.g., the data state being verified by the prior verify phase of the programming operation.

[0164] FIGS. **16**A-**16**B are a flowchart of a method of operating a memory in accordance with an embodiment. The method might represent actions associated with a programming operation, e.g., portions of a verify phase and programming phase of the programming operation, performed by the memory. The method might be in the form of computer-readable instructions, e.g., stored to the instruction registers **128**. Such computer-readable instructions might be executed by a controller, e.g., the control logic **116**, to cause the relevant components of the memory to perform the method.

[0165] At **1641**, a data line and a node (e.g., of a page buffer circuit) might be precharged to a first voltage level for a verify phase of a programming operation. This might correspond to times t**0**-t**2** of FIG. **10**. The first voltage level might correspond to the voltage level **1032** of FIG. **10** where the optional discharge of the data line and node is utilized, or the voltage level **1030** where it is not. The verify phase might seek to verify a particular data state, which might correspond to any one of the data states L1-L7 for a TLC memory, or any one of the data states L1-L15 for a QLC memory, for example.

[0166] At **1643**, the node might be isolated from the data line. This might correspond to time t**2** of FIG. **10**. At **1645**, the data line might be selectively discharged in response to a threshold voltage level of a memory cell connected to the data line. This might correspond to times t**2**-t**3** of FIG. **10**. At **1647**, a boost voltage level might be capacitively coupled to the node. This might further correspond to times t**2**-t**3** of FIG. **10**.

[0167] At **1649**, the node might be connected to the data line. This might correspond to time t**3** of FIG. **10**. At **1651**, the node might be isolated from the data line. This might correspond to time t**4** of FIG. **10**.

[0168] At **1653**, a deboost voltage level, lower than the boost voltage level, might be capacitively coupled to the node. This might correspond to times t**9**-t**10** of FIG. **10**. Note that additional deboost voltage levels might be previously capacitively coupled to the node.

[0169] At **1655**, a control gate of a transistor that is connected to the node might be electrically floated, e.g., while the node is capacitively coupled to the deboost voltage level. The transistor might correspond to the transistor **447** of FIG. **4**A, the transistor **1150** of FIG. **11**A, or the transistor **1160** of FIG. **11**B, for example. The control gate of the transistor **447** might be connected to the tc signal node **432** by activating the transistors **439**, **435**, and **419**, and might then be electrically floated by deactivating the transistor **449**. The control gates of the transistors **1150** and **1160** might be directly connected to the tc signal node **432**, and might be electrically floated by deactivating the transistors **411** and **419**.

[0170] At **1657**, a first source/drain of the transistor might be connected to a data line corresponding to the memory cell while applying a second voltage level to a second source/drain of the transistor and while continuing to electrically float the control gate of the transistor. The second voltage level might correspond to (e.g., be equal to) an inhibit voltage level of the programming operation. For other embodiments, the second voltage level might be higher than the inhibit voltage level.

[0171] At **1659**, a third voltage level might be applied to the control gate of the memory cell while the data line is connected to the first source/drain of the transistor, wherein the third voltage level is configured to increase a threshold voltage of the memory cell. The third voltage level might be a voltage level of a programming pulse determined in response to a value of VgVt for a group of memory cells, e.g., a group of memory cells having a same desired data state for the programming operation, resulting from a prior (e.g., immediately prior) programming pulse, and a desired threshold voltage for that desired data state.

[0172] FIGS. **17**A-**17**C are a flowchart of a method of operating a memory in accordance with an embodiment. The method might represent actions associated with a programming operation, e.g., portions of a verify phase and programming phase of the programming operation, performed by the memory. The method might be in the form of computer-readable instructions, e.g., stored to the instruction registers **128**. Such computer-readable instructions might be executed by a controller, e.g., the control logic **116**, to cause the relevant components of the memory to perform the method.
[0173] At **1771**, a data line and a node (e.g., of a page buffer circuit) might be precharged to a first voltage level for a verify phase of a programming operation. This might correspond to times t**0**-t**2** of FIG. **10**. The first voltage level might correspond to the voltage level **1032** of FIG. **10** where the optional discharge of the data line and node is utilized, or the voltage level **1030** where it is not.
[0174] At **1773**, the node might be isolated from the data line. This might correspond to time t**2** of FIG. **10**. At **1775**, the data line might be selectively discharged in response to a threshold voltage level of a memory cell connected to the data line. This might correspond to times t**2**-t**3** of FIG. **10**. At **1777**, a boost voltage level might be capacitively coupled to the node. This might further correspond to times t**2**-t**3** of FIG. **10**.
[0175] At **1779**, the node might be connected to the data line. This might correspond to time t**3** of FIG. **10**. At **1781**, the node might be isolated from the data line. This might correspond to time t**4** of FIG. **10**.
[0176] At **1783**, a first deboost voltage level, lower than the boost voltage level, might be capacitively coupled to the node. This might correspond to times t**5**-t**6** of FIG. **10**. At **1785**, the memory cell might be identified to be fully enabled for programming for a subsequent programming phase of the programming operation in response to a voltage level of the node being lower than a threshold (e.g., a predetermined voltage level) while capacitively coupling the first deboost voltage level to the node. This might correspond to times t**6**-t**7** of FIG. **10**. For example, the node might correspond to the tc signal node **432** of the page buffer circuit **400**. The threshold might correspond to the threshold voltage level of the transistor **451** of the page buffer circuit **400**. In this manner, if the transistor **451** is deemed to be deactivated in response to the voltage level of the tc signal node **431** while the first deboost voltage level is capacitively coupled to the tc signal node **432**, the voltage level of the tc signal node **432** might be deemed to be lower than the threshold. A memory cell identified to be fully enabled for programming for a subsequent programming phase of the programming operation might be configured to receive the enable voltage on its corresponding data line for the subsequent programming phase.
[0177] At **1787**, a second deboost voltage level, lower than the first deboost voltage level, might be capacitively coupled to the node. This might correspond to times t**7**-t**8** of FIG. **10**. At **1789**, the memory cell might be identified to be inhibited from programming for the subsequent programming phase of the programming operation in response to the voltage level of the node being higher than or equal to the threshold while capacitively coupling the second deboost voltage level to the node. This might correspond to times t**8**-t**9** of FIG. **10**. Continuing with the foregoing example, if the transistor **451** is deemed to be activated in response to the voltage level of the tc signal node **431** while the second deboost voltage level is capacitively coupled to the tc signal node **432**, the voltage level of the tc signal node **432** might be deemed to be higher than or equal to the threshold. A memory cell identified to be inhibited from programming for a subsequent programming phase of the programming operation might be configured to receive the inhibit voltage on its corresponding data line for the subsequent programming phase.
[0178] At **1791**, the memory cell might be identified to be partially enabled for programming for the subsequent programming phase of the programming operation in response to the voltage level of the node being higher than or equal to the threshold while capacitively coupling the first deboost voltage level to the node, and lower than the threshold while capacitively coupling the second deboost voltage level to the node. This might correspond to times t**5**-t**6** and times t**8**-t**9** of FIG. **10**. Continuing with the foregoing example, if the transistor **451** is deemed to be activated in response

to the voltage level of the tc signal node **431** while the first deboost voltage level is capacitively coupled to the tc signal node **432**, and the transistor **451** is deemed to be deactivated in response to the voltage level of the tc signal node **431** while the second deboost voltage level is capacitively coupled to the tc signal node **432**, the voltage level of the tc signal node **432** might be deemed to be higher than or equal to the threshold while the first deboost voltage level is capacitively coupled to the node, and lower than the threshold while the second deboost voltage level is capacitively coupled to the node. A memory cell identified to be partially enabled for programming for a subsequent programming phase of the programming operation might be configured to receive a voltage level on its corresponding data line for the subsequent programming phase that is between the enable voltage and the inhibit voltage.

[0179] At **1793**, a third deboost voltage level, lower than the second deboost voltage level, might be capacitively coupled to the node. This might correspond to times t**9**-t**10** of FIG. **10**. At **1795**, a control gate of a transistor that is connected to the node might be electrically floated, e.g., while the node is capacitively coupled to the third deboost voltage level. The transistor might correspond to the transistor **447** of FIG. **4**A, the transistor **1150** of FIG. **11**A, or the transistor **1160** of FIG. **11**B, for example.

[0180] At **1797**, a first source/drain of the transistor might be connected to a data line corresponding to the memory cell while applying a second voltage level to a second source/drain of the transistor and while continuing to electrically float the control gate of the transistor. The second voltage level might correspond to (e.g., be equal to) an inhibit voltage level of the programming operation. For other embodiments, the second voltage level might be higher than the inhibit voltage level.

[0181] At **1799**, a third voltage level might be applied to the control gate of the memory cell while the data line is connected to the first source/drain of the transistor, wherein the third voltage level is configured to increase a threshold voltage of the memory cell. The third voltage level might be a voltage level of a programming pulse determined in response to a value of VgVt for a group of memory cells, e.g., a group of memory cells having a same desired data state for the programming operation, resulting from a prior (e.g., immediately prior) programming pulse, and a desired threshold voltage for that desired data state. The processing of **1793-1799** might be performed in response to identifying the memory cell to be partially enabled for programming for the subsequent programming phase of the programming operation.

[0182] The methods of FIGS. **13-17**C might be performed multiple times during a programming operation, each time for memory cells having a different desired data state for the programming operation. For example, the method of FIG. **13** might be performed for memory cells to be programmed to the L1 data state from the verify pulse **804**.sub.1 to the programming pulse **802**.sub.1, might be performed for memory cells to be programmed to the L2 data state from the verify pulse **804**.sub.2 to the programming pulse **802**.sub.2, might be performed for memory cells to be programmed to the L3 data state from the verify pulse **804**.sub.3 to the programming pulse **802**.sub.3, and so on. Such a sequence could similarly be used for the method of FIG. **14**, the method of FIG. **15**, the method of FIGS. **16**A-**16**B, and the method of FIGS. **17**A-**17**C.

[0183] FIG. **18** is a schematic of portions of an array of memory cells in accordance with additional embodiments. Like numbered elements in FIG. **18** correspond to the description as provided with respect to prior figures. It is recognized that various embodiments might be expected to apply a number of different voltage levels to data lines during a programming operation. As such, there may be a concern of interference, or coupling, between adjacent data lines. Where shielding is not available, e.g., programming involves every other data line, a weak pull-down could be applied to a data line receiving its voltage level through a source-follower transistor. FIG. **18** depicts two blocks of memory cells, e.g., a selected block of memory cells **250**.sub.0 and an unselected block of memory cells **2501**, that share a data line **204**. A memory cell **208**, e.g., memory cell **208**.sub.X0, of the block of memory cells **250**.sub.0 might be selected for programming, and might be identified

to be partially enabled for programming. As such, during its programming pulse, the data line might be connected to a source-follower transistor, e.g., transistor **447**, transistor **1150**, or transistor **1160**, while a voltage node, e.g., voltage node **448**, voltage node **418**, or voltage node **1162**, respectively, is configured to receive its voltage level.

[0184] While the data line **204** is connected to its source-follower transistor, the data line **204** might be connected to the common source **2161**. For example, each drain select line, e.g., drain select lines **215**.sub.20, **215**.sub.10, and **215**.sub.00, might receive a voltage level sufficient to activate a corresponding drain select gate, e.g., drain select gate **212**.sub.20, **212**.sub.10, and **212**.sub.00, respectively, while each access line **202** of the NAND strings **206** of the block of memory cells **2501** receives a voltage level sufficient to activate a corresponding memory cell **208**, and while each source select line, e.g., source select line **214**.sub.1, receives a voltage level sufficient to activate a corresponding source select gate, e.g., source select gate **210**.sub.1. In this manner, a pull-down current might be established through an unselected block of memory cells. The pull-down current might be applied for the duration of the data line **204** receiving its voltage level from the source-follower transistor. For other embodiments, the pull-down current might be removed, e.g., isolating the data line **204** from the common source **2161**, after a steady-state voltage level is established on the data line **204**.

CONCLUSION

[0185] Although specific embodiments have been illustrated and described herein, it will be appreciated by those of ordinary skill in the art that any arrangement that is calculated to achieve the same purpose might be substituted for the specific embodiments shown. Many adaptations of the embodiments will be apparent to those of ordinary skill in the art. Accordingly, this application is intended to cover any adaptations or variations of the embodiments.

Claims

1. A memory, comprising: an array of memory cells; and a controller for access of the array of memory cells, wherein the controller is configured to cause the memory to: precharge a data line and a node to a first voltage level; isolate the node from the data line, then capacitively couple a boost voltage level to the node; selectively discharge the data line through a memory cell of the array of memory cells in response to applying a second voltage level to a control gate of the memory cell; connect the node to the data line, then isolate the node from the data line; capacitively couple a deboost voltage level, lower than the boost voltage level, to the node; electrically float a control gate of a transistor that is connected to the node; connect a first source/drain of the transistor to the data line while applying a third voltage level to a second source/drain of the transistor and while continuing to electrically float the control gate of the transistor; and apply a fourth voltage level to the control gate of the memory cell while the data line is connected to the first source/drain of the transistor, wherein the fourth voltage level is configured to increase a threshold voltage level of the memory cell.

2. The memory of claim 1, wherein the second voltage level is a voltage level of a verify pulse of a programming operation for a desired data state of the memory cell.

3. The memory of claim 2, wherein the fourth voltage level is a voltage level of a programming pulse of the programming operation.

4. The memory of claim 1, wherein the controller is further configured to cause the memory to apply a pull-down current to the data line while the data line is connected to the first source/drain of the transistor.

5. The memory of claim 4, wherein the controller is further configured to cause the memory to remove the pull-down current from the data line after a steady-state voltage level is established on the data line.

6. The memory of claim 1, wherein the controller being configured to cause the memory to

precharge the data line and the node to the first voltage level comprises the controller being configured to cause the memory to precharge the data line and the node to a fifth voltage level higher than the first voltage level, and to discharge the node to the first source/drain of the transistor while the second source/drain of the transistor is configured to receive an inhibit voltage level of the programming operation and while the gate of the transistor is connected to the node.

7. The memory of claim 1, wherein the deboost voltage level is a third deboost voltage level, wherein the memory cell is a first memory cell of the array of memory cells, wherein the data line is a first data line, wherein the node is a node of a first page buffer circuit of the memory, wherein the transistor is a first transistor, and wherein the controller is further configured to cause the memory to: precharge a second data line and a node of a second page buffer circuit of the memory to the first voltage level concurrently with precharging the first data line and the node of the first page buffer circuit to the first voltage level; precharge a third data line and a node of a third page buffer circuit of the memory to the first voltage level concurrently with precharging the first data line and the node of the first page buffer circuit to the first voltage level; isolate the node of the second page buffer circuit from the second data line, then capacitively couple the boost voltage level to the node of the second page buffer circuit; isolate the node of the third page buffer circuit from the second third line, then capacitively couple the boost voltage level to the node of the third page buffer circuit; selectively discharge the second data line through a second memory cell of the array of memory cells in response to applying the second voltage level to a control gate of the second memory cell; selectively discharge the third data line through a third memory cell of the array of memory cells in response to applying the second voltage level to a control gate of the third memory cell; connect the node of the second page buffer circuit to the second data line, then isolate the node of the second page buffer circuit from the second data line; connect the node of the third page buffer circuit to the third data line, then isolate the node of the third page buffer circuit from the third data line; capacitively couple a first deboost voltage level, lower than the boost voltage level and higher than the third deboost voltage level, to the node of the first page buffer circuit, to the node of the second page buffer circuit, and to the node of the third page buffer circuit, prior to capacitively coupling the third deboost voltage level to the node of the first page buffer circuit; capacitively couple a second deboost voltage level, lower than the first deboost voltage level and higher than the third deboost voltage level, to the node of the first page buffer circuit, to the node of the second page buffer circuit, and to the node of the third page buffer circuit, after coupling the first deboost voltage level to the node of the first page buffer circuit, to the node of the second page buffer circuit, and to the node of the third page buffer circuit, and prior to capacitively coupling the third deboost voltage level to the node of the first page buffer circuit; apply the fourth voltage level to the control gate of the first memory cell while the first data line is connected to the first source/drain of the first transistor in response to a voltage level of the node of the first page buffer circuit being higher than or equal to a threshold while capacitively coupling the first deboost voltage level to the node of the first page buffer circuit and lower than the threshold while capacitively coupling the second deboost voltage level to the node of the first page buffer circuit; and apply the fourth voltage level to the control gate of the second memory cell while the second data line is connected to receive an enable voltage of the programming operation in response to a voltage level of the node of the second page buffer circuit being lower than the threshold while capacitively coupling the first deboost voltage level to the node of the second page buffer circuit; apply the fourth voltage level to the control gate of the third memory cell while the third data line is connected to receive an inhibit voltage of the programming operation in response to a voltage level of the node of the third page buffer circuit being higher than or equal to the threshold while capacitively coupling the first deboost voltage level to the node of the second page buffer circuit.

8. A memory, comprising: an array of memory cells; and a controller for access of the array of memory cells, wherein the controller is configured to cause the memory to: precharge a data line and a node to a first voltage level for a verify phase of a programming operation; isolate the node

from the data line; selectively discharge the data line in response to a threshold voltage level of a memory cell connected to the data line; capacitively couple a boost voltage level to the node; connect the node to the data line; isolate the node from the data line; capacitively couple a first deboost voltage level, lower than the boost voltage level, to the node; identify the memory cell to be fully enabled for programming for a subsequent programming phase of the programming operation in response to a voltage level of the node being lower than a threshold while capacitively coupling the first deboost voltage level to the node; capacitively couple a second deboost voltage level, lower than the first deboost voltage level, to the node; identify the memory cell to be inhibited from programming for the subsequent programming phase of the programming operation in response to the voltage level of the node being higher than or equal to the threshold while capacitively coupling the second deboost voltage level to the node; identify the memory cell to be partially enabled for programming for the subsequent programming phase of the programming operation in response to the voltage level of the node being higher than or equal to the threshold while capacitively coupling the first deboost voltage level to the node and lower than the threshold while capacitively coupling the second deboost voltage level to the node; capacitively couple a third deboost voltage level, lower than the second deboost voltage level, to the node; and in response to identifying the memory cell to be partially enabled for programming for the subsequent programming phase of the programming operation: electrically float a control gate of a transistor that is connected to the node; connect a first source/drain of the transistor to the data line while applying a second voltage level to a second source/drain of the transistor and while electrically floating the control gate of the transistor; and apply a third voltage level to a control gate of the memory cell while the data line is connected to the first source/drain of the transistor, wherein the third voltage level is configured to increase a threshold voltage level of the memory cell.

9. The memory of claim 8, wherein the controller is further configured to cause the memory to: in response to identifying the memory cell to be inhibited from programming for the subsequent programming phase of the programming operation: apply the third voltage level to the control gate of the memory cell while the data line is connected to receive an inhibit voltage level of the programming operation.

10. The memory of claim 9, wherein the controller is further configured to cause the memory to: in response to identifying the memory cell to be fully enabled for programming for the subsequent programming phase of the programming operation: apply the third voltage level to the control gate of the memory cell while the data line is connected to receive an enable voltage level of the programming operation.

11. The memory of claim 10, wherein the memory cell is a particular memory cell of a plurality of memory cells selected for programming during the programming operation, wherein the memory cell has a particular target data state of a plurality of target data states for the programming operation, and wherein the controller is further configured to cause the memory to: for each memory cell of the plurality of memory cells selected for programming during the programming operation and having a target data state of the plurality of target data states that is higher than the particular target data state, apply the third voltage level to a control gate of that memory cell while a data line corresponding to that memory cell is connected to receive the enable voltage level of the programming operation.

12. The memory of claim 11, wherein the controller is further configured to cause the memory to: for each memory cell of the plurality of memory cells selected for programming during the programming operation and having a target data state of the plurality of target data states that is lower than the particular target data state, apply the third voltage level to a control gate of that memory cell while a data line corresponding to that memory cell is connected to receive the inhibit voltage level of the programming operation.

13. The memory of claim 8, wherein the memory cell is a particular memory cell of a plurality of memory cells selected for programming during the programming operation, wherein the memory

cell has a particular target data state of a plurality of target data states for the programming operation, and wherein the controller is further configured to cause the memory to: for each memory cell of the plurality of memory cells selected for programming during the programming operation and having a target data state of the plurality of target data states that is higher than or equal to the particular target data state: precharge a respective data line for that memory cell and a respective node for that memory cell to the first voltage level for the verify phase of the programming operation; isolate the respective node from the respective data line; selectively discharge the respective data line in response to a threshold voltage level of that memory cell connected to the respective data line; capacitively couple the boost voltage level to the respective node; connect the respective node to the respective data line; isolate the respective node from the respective data line; capacitively couple the first deboost voltage level to the respective node; and capacitively couple the second deboost voltage level to the respective node; determine a first number of memory cells of the plurality of memory cells selected for programming whose respective node has a voltage level lower than a threshold while capacitively coupling the first deboost voltage level to the respective nodes; determine a second number of memory cells of the plurality of memory cells selected for programming whose respective node has a voltage level higher than or equal to the threshold while capacitively coupling the second deboost voltage level to the respective nodes; and determine a representative value of VgVt for the plurality of memory cells selected for programming during the programming operation and having target data states higher than or equal to the particular target data state; and determine a value of the third voltage level in response to the determined representative value of VgVt and a desired threshold voltage level corresponding to the particular data state.

14. A memory, comprising: an array of memory cells; a plurality of data lines, wherein each data line of the plurality of data lines is selectively connected to a respective plurality of memory cells of the array of memory cells; a page buffer circuit connected to a particular data line of the plurality of data lines; and a controller for access of the array of memory cells, wherein the controller, during a programming operation of the memory, is configured to cause the memory to: precharge the particular data line and a node of the page buffer circuit to a first voltage level during a verify phase of the programming operation; isolate the node from the particular data line, then capacitively couple a boost voltage level to the node; selectively discharge the particular data line through a memory cell of its respective plurality of memory cells in response to applying a second voltage level to a control gate of the memory cell; connect the node to the particular data line, then isolate the node from the particular data line; capacitively couple a deboost voltage level, lower than the boost voltage level, to the node; electrically float a control gate of a transistor of the page buffer circuit that is connected to the node; connect a first source/drain of the transistor to the particular data line while applying an inhibit voltage level of the programming operation to a second source/drain of the transistor and while continuing to electrically float the control gate of the transistor; and during a subsequent programming phase of the programming operation, apply a third voltage level to the control gate of the memory cell while the particular data line is connected to the first source/drain of the transistor, wherein the third voltage level is configured to increase a threshold voltage level of the memory cell.

15. The memory of claim 14, wherein the second voltage level is configured to activate the memory cell in response to a threshold voltage level of the memory cell being lower than a target threshold voltage level of the memory cell for the programming operation, and to deactivate the memory cell in response to the threshold voltage level of the memory cell being higher than the target threshold voltage level of the memory cell.

16. The memory of claim 14, wherein the control gate of the transistor is directly connected to the node.

17. The memory of claim 14, wherein the deboost voltage level is a third deboost voltage level, and wherein the controller, during the verify phase of the programming operation, is further configured

to cause the memory to: prior to capacitively coupling the third deboost voltage level to the node: capacitively couple a first deboost voltage level, lower than the boost voltage level and higher than the third deboost voltage level, to the node; and capacitively couple a second deboost voltage level, lower than the first deboost voltage level and higher than the third deboost voltage level, to the node; and in response to a voltage level of the node being higher than or equal to a threshold while capacitively coupling the first deboost voltage level to the node, and the voltage level of the node being lower than the threshold while capacitively coupling the second deboost voltage level to the node, identifying the memory cell to be partially enabled for programming during the subsequent programming phase of the programming operation.

18. The memory of claim 17, wherein the node is a first node, wherein the memory cell is a first memory cell, wherein the transistor is a first transistor, and wherein the memory further comprises: a second page buffer circuit connected to a second data line of the plurality of data lines; wherein the controller, during the programming operation, is further configured to cause the memory to: precharge the second data line and a second node of the second page buffer circuit to a fourth voltage level during the verify phase of the programming operation; isolate the second node from the second data line, then capacitively couple the boost voltage level to the second node; selectively discharge the second data line through a second memory cell of its respective plurality of memory cells in response to applying the second voltage level to the control gate of the second memory cell, wherein a target threshold voltage level of the second memory cell for the programming operation is equal to the target threshold voltage level of the first memory cell, and wherein the control gate of the second memory cell is connected to the control gate of the first memory cell; connect the second node to the second data line, then isolate the second node from the second data line; capacitively couple the first deboost voltage level to the second node; capacitively couple the second deboost voltage level to the second node; capacitively couple the third deboost voltage level to the second node; in response to a voltage level of the second node being lower than the threshold while capacitively coupling the first deboost voltage level to the second node: apply an enable voltage level of the programming operation to the second data line during the subsequent programming phase of the programming operation; and apply the third voltage level to the control gate of the second memory cell while applying the enable voltage level to the second data line and while applying the third voltage level to the control gate of the first memory cell while the particular data line is connected to the first source/drain of the first transistor; in response to the voltage level of the second node being higher than or equal to the threshold while capacitively coupling the second deboost voltage level to the second node: apply the inhibit voltage level to the second data line during the subsequent programming phase of the programming operation; and apply the third voltage level to the control gate of the second memory cell while applying the inhibit voltage level to the second data line, and while applying the third voltage level to the control gate of the first memory cell while the particular data line is connected to the first source/drain of the first transistor; and in response to the voltage level of the second node being higher than or equal to the threshold while capacitively coupling the first deboost voltage level to the second node, and lower than the threshold while capacitively coupling the second deboost voltage level to the second node: electrically float a control gate of a second transistor of the second page buffer circuit that is connected to the second node; connect a first source/drain of the second transistor to the second data line while applying the inhibit voltage level to a second source/drain of the second transistor and while continuing to electrically float the control gate of the second transistor; and during the subsequent programming phase of the programming operation, apply the third voltage level to the control gate of the second memory cell while the second data line is connected to the first source/drain of the second transistor.

19. The memory of claim 18, wherein the fourth voltage level is higher than the inhibit voltage level and equal to the first voltage level.

20. The memory of claim 18, wherein the first voltage level corresponds to the inhibit voltage level

plus a threshold voltage level of the first transistor, and wherein the fourth voltage level corresponds to the inhibit voltage level plus a threshold voltage level of the second transistor.